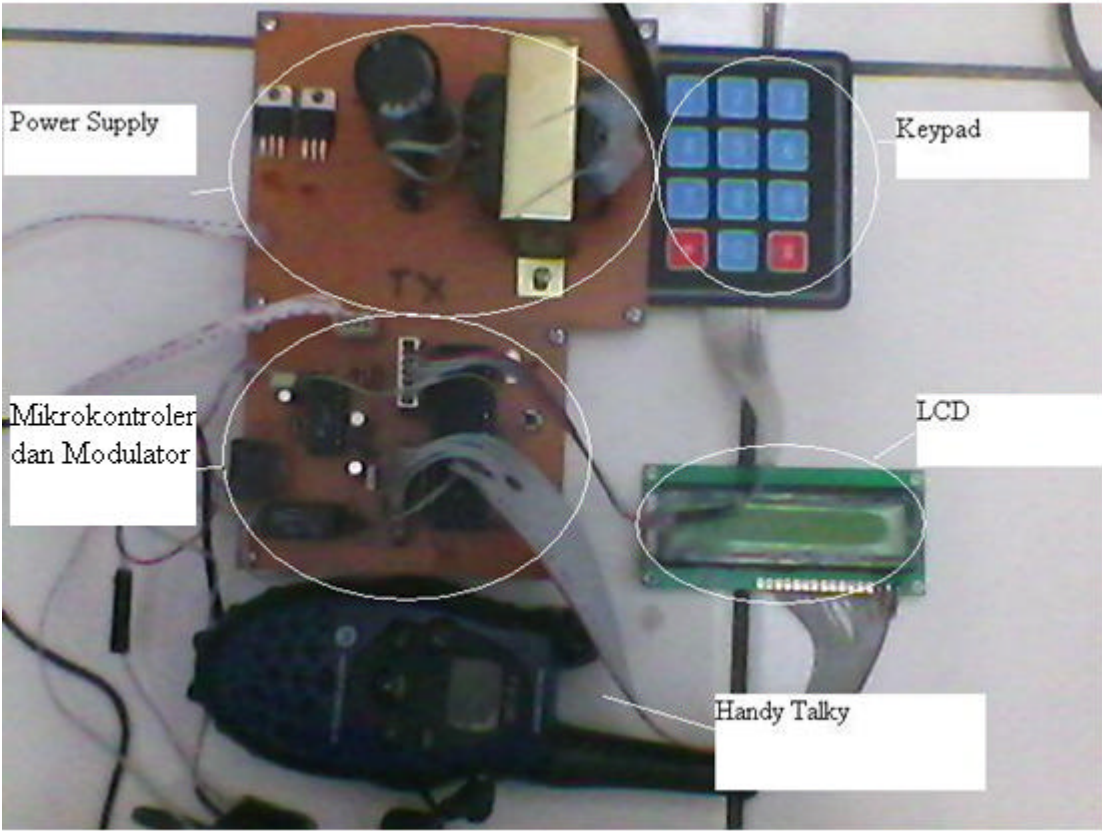
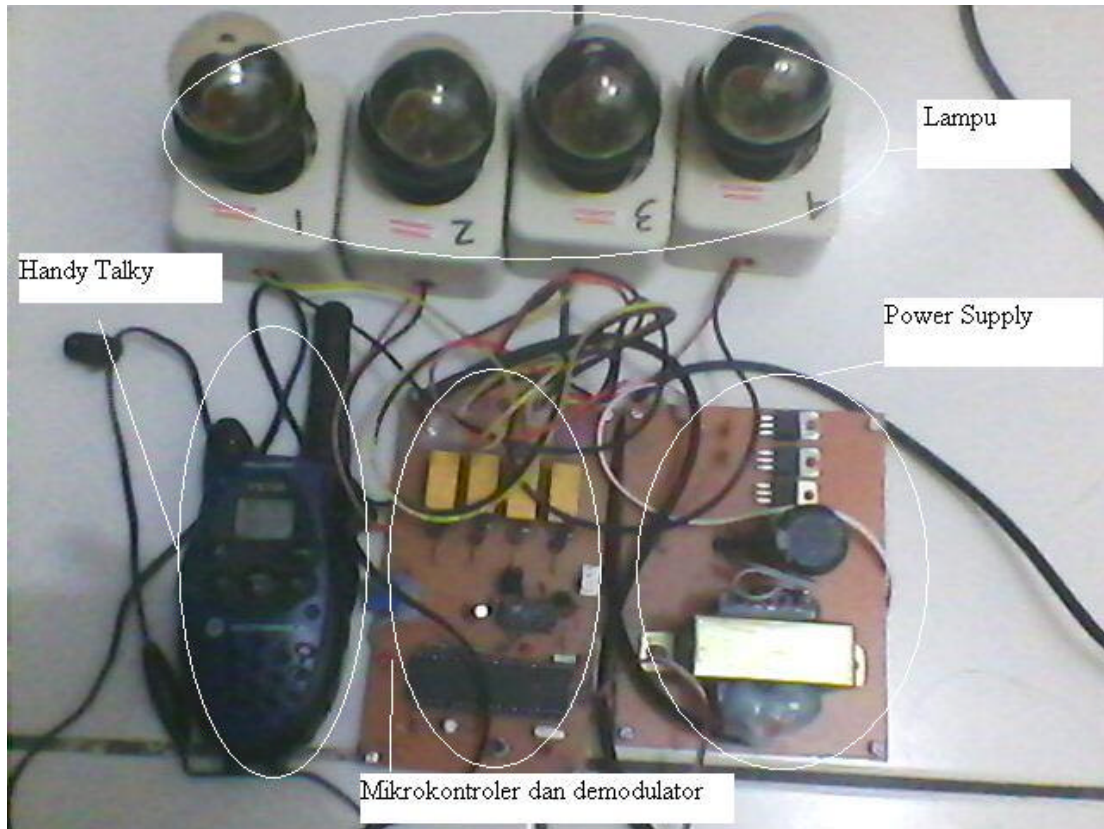


LAMPIRAN A
FOTO ALAT SISTEM PENGENDALI *ON-OFF*

BAGIAN REMOTE CONTROL



BAGIAN SISTEM PLANT



LAMPIRAN B
PROGRAM PADA PENGONTROL ATMEL

PROGRAM PADA BAGIAN REMOTE CONTROL

```
#INCLUDE "8051.H"

RELAYPTT .EQU P2.7
E_LCD .EQU P1.0
RW_LCD .EQU P1.1
RS_LCD .EQU P1.2
DATA_LCD .EQU P0

SWITCH .EQU P2
X1 .EQU P2.4
X2 .EQU P2.5
X3 .EQU P2.6
Y1 .EQU P2.0
Y2 .EQU P2.1
Y3 .EQU P2.2
Y4 .EQU P2.3

.ORG $30
DATAKEY .BLOCK 1
DATAKIRIM .BLOCK 1
.ORG $0
LJMP MULAI

.ORG $100
MULAI: MOV SP,#$20
MOV PSW,#0
LCALL DELAYSW
CLR RELAYPTT
LCALL INIT_LCD
LCALL INITSERIAL
MOV DPTR,#TEXT1
LCALL PROC_STRTOLCD
LCALL PROC_LFLCD
MOV DPTR,#TEXT2
LCALL PROC_STRTOLCD
LCALL DELAYSW
LCALL DELAYSW
LCALL DELAYSW
LCALL DELAYSW
LCALL DELAYSW
LCALL DELAYSW
LCALL DELAYSW

LOOP: MOV SP,#$20
LCALL PROC_CLEARLCD
MOV DPTR,#TEXTPERINTAH1
LCALL PROC_STRTOLCD
LCALL PROC_LFLCD
MOV DPTR,#TEXTPERINTAH2
LCALL PROC_STRTOLCD
```

ULANGI:

```
LCALL CEKKEYPAD
LCALL KEYPADTOLCD
```

```
SETB RELAYPTT
LCALL DELAY5X
```

```
MOV R1,#2
```

ULANGKIRIM0:

```
MOV A,#$55
LCALL SENDCHR
MOV A,#$EE
LCALL SENDCHR
MOV A,#$AA
LCALL SENDCHR
```

```
MOV R2,#200
```

ULANGKIRIM1:

```
MOV A,DATAKIRIM
LCALL SENDCHR
MOV A,#$0D
LCALL SENDCHR
DJNZ R2,ULANGKIRIM1
DJNZ R1,ULANGKIRIM0
```

```
LCALL DELAYSW
LCALL DELAYSW
CLR RELAYPTT
```

LOOPUL: LJMPL LOOP

```
CEKKEYPAD: LCALL SCANNINGKEYPAD
CJNE A,#$0,CEKKEYPASS
LJMP CEKKEYPAD
CEKKEYPASS: RET
```

PROC_HOMELCD:

```
MOV A,#02H
LCALL WRITE_CTRLLCD
RET
```

; ROUTINE LF LCD MENEMPATKAN KURSUSOR PADA BARIS KE 2 LCD

PROC_LFLCD:

```
MOV A,#0C0H
LCALL WRITE_CTRLLCD
RET
```

; ROUTINE CLEAR LCD MENGHAPUS LAYAR LCD

PROC_CLEARLCD:

```
MOV A,#01H
LCALL WRITE_CTRLLCD
```

RET

; ROUTINE PENULISAN DATA KE LCD

WRITE_DATA_LCD:

MOV DATA_LCD,A

CLR RW_LCD
SETB RS_LCD
CLR E_LCD
LCALL DELAY_LCD

CLR RW_LCD
SETB RS_LCD
SETB E_LCD
LCALL DELAY_LCD

CLR RW_LCD
SETB RS_LCD
CLR E_LCD
NOP
SETB RW_LCD
CLR RS_LCD
CLR E_LCD
LCALL DELAY_LCD
RET

; ROUTINE PENULISAN PERINTAH/COMMAND KE LCD

WRITE_CTRL_LCD:

; RW RS E
; 0 1 0

MOV DATA_LCD,A

CLR RW_LCD
CLR RS_LCD
CLR E_LCD
LCALL DELAY_LCD

CLR RW_LCD
CLR RS_LCD
SETB E_LCD
LCALL DELAY_LCD

CLR RW_LCD
CLR RS_LCD
CLR E_LCD
NOP
SETB RW_LCD
CLR RS_LCD
CLR E_LCD
LCALL DELAY_LCD

RET

```
;-----  
; Routine Pengiriman String ke Display LCD  
;-----
```

```
PROC_STRTOLCD:
```

```
CLR A  
MOVC A,@A+DPTR  
CJNE A,#00H,STRTOLCD  
RET
```

```
STRTOLCD:
```

```
LCALL WRITE_DATA_LCD  
INC DPTR  
SJMP PROC_STRTOLCD
```

```
;-----  
; ROUTINE INISIALISASI LCD  
;-----
```

```
INIT_LCD:
```

```
MOV A,#38H  
LCALL WRITE_CTRL_LCD  
MOV A,#0EH  
LCALL WRITE_CTRL_LCD  
MOV A,#0CH  
LCALL WRITE_CTRL_LCD  
MOV A,#06H  
LCALL WRITE_CTRL_LCD  
MOV A,#01H  
LCALL WRITE_CTRL_LCD  
RET
```

```
INITSERIAL:
```

```
MOV TMOD,#20H  
MOV TCON,#41H  
MOV TH1,#$D0  
MOV SCON,#50H  
RET
```

```
SENDCHR:
```

```
CLR TI  
MOV SBUF,A
```

```
TXLOOP:
```

```
JNB TI,TXLOOP  
RET
```

```
ANDF0LCD: SWAP A
```

```
AND0FLCD:
```

```
ANL A,#$0F  
ADD A,#$30  
LCALL WRITE_DATA_LCD  
RET
```

```
SCANNINGKEYPAD:
```

```
KOLOM1: MOV DATAKEY,#0  
CLR X1  
SETB X2  
SETB X3
```



```

        MOV     A,SWITCH
        ANL     A,#0FH
CTOMBOL1:  CJNE  A,#0EH,CTOMBOL4
        MOV     DATAKEY,#01H
        MOV     DATAKIRIM,#$1
        LJMP   TOLCD
CTOMBOL4:  CJNE  A,#0DH,CTOMBOL7
        MOV     DATAKEY,#04H
        MOV     DATAKIRIM,#$4
        LJMP   TOLCD
CTOMBOL7:  CJNE  A,#0BH,CTOMBOLB
        MOV     DATAKEY,#07H
        MOV     DATAKIRIM,#$7
        LJMP   TOLCD
CTOMBOLB:  CJNE  A,#07H,KOLOM2
        MOV     DATAKEY,#0BH
        MOV     DATAKIRIM,#'B'
        LJMP   TOLCD

KOLOM2:    SETB  X1
        CLR    X2
        SETB  X3
        MOV     A,SWITCH
        ANL     A,#0FH
CTOMBOL2:  CJNE  A,#0EH,CTOMBOL5
        MOV     DATAKEY,#02H
        MOV     DATAKIRIM,#$2
        LJMP   TOLCD
CTOMBOL5:  CJNE  A,#0DH,CTOMBOL8
        MOV     DATAKEY,#05H
        MOV     DATAKIRIM,#$5
        LJMP   TOLCD
CTOMBOL8:  CJNE  A,#0BH,CTOMBOL0
        MOV     DATAKEY,#08H
        MOV     DATAKIRIM,#$8
        LJMP   TOLCD
CTOMBOL0:  CJNE  A,#07H,KOLOM3
        MOV     DATAKEY,#0AH
        MOV     DATAKIRIM,#$0
        LJMP   TOLCD

KOLOM3:    SETB  X1
        SETB  X2
        CLR    X3
        MOV     A,SWITCH
        ANL     A,#0FH
CTOMBOL3:  CJNE  A,#0EH,CTOMBOL6
        MOV     DATAKEY,#03H
        MOV     DATAKIRIM,#$3
        LJMP   TOLCD
CTOMBOL6:  CJNE  A,#0DH,CTOMBOL9
        MOV     DATAKEY,#06H
        MOV     DATAKIRIM,#$6
        LJMP   TOLCD
CTOMBOL9:  CJNE  A,#0BH,CTOMBOLP
        MOV     DATAKEY,#09H
        MOV     DATAKIRIM,#$9
        LJMP   TOLCD

```

```

CTOMBOLP:  CJNE  A,#07H,KEYPADRET
            MOV  DATAKEY,#0CH
            MOV  DATAKIRIM,#'P'
TOLCD:
            LCALL DELAYSW
            MOV  A,DATAKEY
            RET
KEYPADRET:  MOV  A,#$0
            RET

KEYPADTOLCD:
            MOV  DPTR,#KEY
            MOV  A,DATAKEY
            MOVC A,@A+DPTR
            LCALL WRITE_DATA_LCD
            RET

DELAY_LCD:  MOV  R7,#04H
D_LCD1:    MOV  R6,#3FH ;4F
D_LCD2:    DJNZ R6,D_LCD2
            DJNZ R7,D_LCD1
            RET

ANDF0:     SWAP  A
AND0F:
            ANL  A,#$0F
            RET

DELAYSW:
            MOV  R5,#02H
DELAYSW0:  MOV  R6,#0FFH
DELAYSW1:  MOV  R7,#0FFH
DELAYSW2:  DJNZ R7,DELAYSW2
            DJNZ R6,DELAYSW1
            DJNZ R5,DELAYSW0
            RET

DELAY5X:
            LCALL DELAYSW
            LCALL DELAYSW
            LCALL DELAYSW
            LCALL DELAYSW
            LCALL DELAYSW
            RET

TEXT1:     .BYTE  " KONTROL GEDUNG ",0
TEXT2:     .BYTE  " - HANDY TALKY - ",0
TEXTPERINTAH1: .BYTE  " M A S U K K A N",0
TEXTPERINTAH2: .BYTE  " PERINTAH= ",0
KEY:       .BYTE  " 1234567890*#"

```

.END

PROGRAM PADA BAGIAN SISTEM PLANT

```
#INCLUDE "8051.H"

RELAY1 .EQU P0.0
RELAY2 .EQU P0.1
RELAY3 .EQU P0.2
RELAY4 .EQU P0.3
LEDSTATUS .EQU P1.0

.ORG $30
DATA .BLOCK 1

.ORG $0
LJMP MULAI

.ORG $100
MULAI: MOV SP,#$20
MOV PSW,#0
LCALL DELAYLED
CLR RELAY1
CLR RELAY2
CLR RELAY3
CLR RELAY4
LCALL INITSERIAL
CLR LEDSTATUS
LCALL DELAYLED
SETB LEDSTATUS
LCALL DELAYLED
CLR LEDSTATUS
LCALL DELAYLED
SETB LEDSTATUS
LCALL DELAYLED
CLR LEDSTATUS
LCALL DELAYLED
SETB LEDSTATUS
LCALL DELAYLED
LJMP LOOP

ISIKANDATA:
MOV DATA,A
LJMP TUNGGUDATA

LOOP: MOV SP,#$20
TUNGGUDATA: CLR RI
LCALL GETCHR
CJNE A,#$0D,ISIKANDATA
CLR LEDSTATUS
LCALL DELAYR
SETB LEDSTATUS
```

```

MOV A,DATA
CEK1:  CJNE A,#$1,CEK2
      SETB RELAY1
      LCALL NYALAKANLED
      LJMPL LOOP
CEK2:  CJNE A,#$2,CEK3
      SETB RELAY2
      LCALL NYALAKANLED
      LJMPL LOOP
CEK3:  CJNE A,#$3,CEK4
      SETB RELAY3
      LCALL NYALAKANLED
      LJMPL LOOP
CEK4:  CJNE A,#$4,CEK5
      SETB RELAY4
      LCALL NYALAKANLED
      LJMPL LOOP
CEK5:  CJNE A,#$5,CEK6
      CLR RELAY1
      LCALL NYALAKANLED
      LJMPL LOOP
CEK6:  CJNE A,#$6,CEK7
      CLR RELAY2
      LCALL NYALAKANLED
      LJMPL LOOP
CEK7:  CJNE A,#$7,CEK8
      CLR RELAY3
      LCALL NYALAKANLED
      LJMPL LOOP
CEK8:  CJNE A,#$8,CEKBINTANG
      CLR RELAY4
      LCALL NYALAKANLED
      LJMPL LOOP
CEKBINTANG: CJNE A,#'B',CEKPAGAR
      SETB RELAY1
      SETB RELAY2
      SETB RELAY3
      SETB RELAY4
      LCALL NYALAKANLED
      LJMPL LOOP
CEKPAGAR: CJNE A,#'P',PASSKODE
      CLR RELAY1
      CLR RELAY2
      CLR RELAY3
      CLR RELAY4
      LCALL NYALAKANLED
      LJMPL LOOP

PASSKODE: CLR RI
          LJMPL LOOP

```

```

INITSERIAL:
MOV TMOD,#20H
MOV TCON,#41H
MOV TH1,#$D0

```

```

MOV   SCON,#50H
RET

GETCHR:  JNB  RI,GETCHR
MOV   A,SBUF
ANL  A,#$7F
CLR  RI
RET

NYALAKANLED: CLR  LEDSTATUS
LCALL DELAYLED
LCALL DELAYLED
LCALL DELAYLED
LCALL DELAYLED
LCALL DELAYLED
LCALL DELAYLED
LCALL DELAYLED
LCALL DELAYLED
LCALL DELAYLED
LCALL DELAYLED
SETB LEDSTATUS
CLR  RI
RET

DELAYR:
DELAYR0:  MOV  R6,#$0F
DELAYR1:  MOV  R7,#$FF
DELAYR2:  DJNZ R7,DELAYR2
        DJNZ R6,DELAYR1
RET

DELAWSW:
MOV  R5,#01H
DELAWSW0:  MOV  R6,#0FFH
DELAWSW1:  MOV  R7,#0FFH
DELAWSW2:  DJNZ R7,DELAWSW2
        DJNZ R6,DELAWSW1
        DJNZ R5,DELAWSW0
RET

DELAYLED:
MOV  R5,#06H
DELAYLED0:  MOV  R6,#0FFH
DELAYLED1:  MOV  R7,#0FFH
DELAYLED2:  DJNZ R7,DELAYLED2
        DJNZ R6,DELAYLED1
        DJNZ R5,DELAYLED0
RET

.END

```

LAMPIRAN C
DATASHEET

Features

- Compatible with MCS-61[®] Products
- 4K Bytes of In-System Programmable (ISP) Flash Memory
 - Endurance: 1000 Write/Erase Cycles
- 4.0V to 5.6V Operating Range
- Fully Static Operation: 0 Hz to 33 MHz
- Three-level Program Memory Look
- 128 x 8-bit Internal RAM
- 32 Programmable I/O Lines
- Two 16-bit Timer/Counters
- Six Interrupt Sources
- Full Duplex UART Serial Channel
- Low-power Idle and Power-down Modes
- Interrupt Recovery from Power-down Mode
- Watchdog Timer
- Dual Data Pointer
- Power-off Flag
- Fast Programming Time
- Flexible ISP Programming (Byte and Page Mode)

Description

The AT89S51 is a low-power, high-performance CMOS 8-bit microcontroller with 4K bytes of In-system programmable Flash memory. The device is manufactured using Atmel's high-density nonvolatile memory technology and is compatible with the industry-standard 80C51 instruction set and pinout. The on-chip Flash allows the program memory to be reprogrammed In-system or by a conventional nonvolatile memory programmer. By combining a versatile 8-bit CPU with In-system programmable Flash on a monolithic chip, the Atmel AT89S51 is a powerful microcontroller which provides a highly-flexible and cost-effective solution to many embedded control applications.

The AT89S51 provides the following standard features: 4K bytes of Flash, 128 bytes of RAM, 32 I/O lines, Watchdog timer, two data pointers, two 16-bit timer/counters, a five-vector two-level interrupt architecture, a full duplex serial port, on-chip oscillator, and clock circuitry. In addition, the AT89S51 is designed with static logic for operation down to zero frequency and supports two software selectable power saving modes. The Idle Mode stops the CPU while allowing the RAM, timer/counters, serial port, and interrupt system to continue functioning. The Power-down mode saves the RAM contents but freezes the oscillator, disabling all other chip functions until the next external interrupt or hardware reset.



8-bit Microcontroller with 4K Bytes In-System Programmable Flash

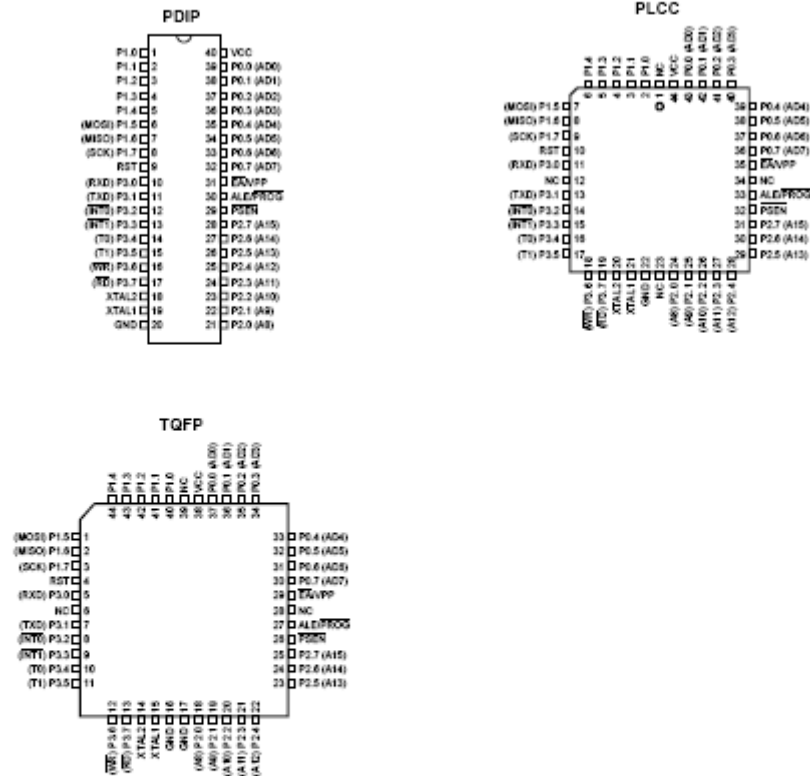
AT89S51

Rev. 2487A-10/01



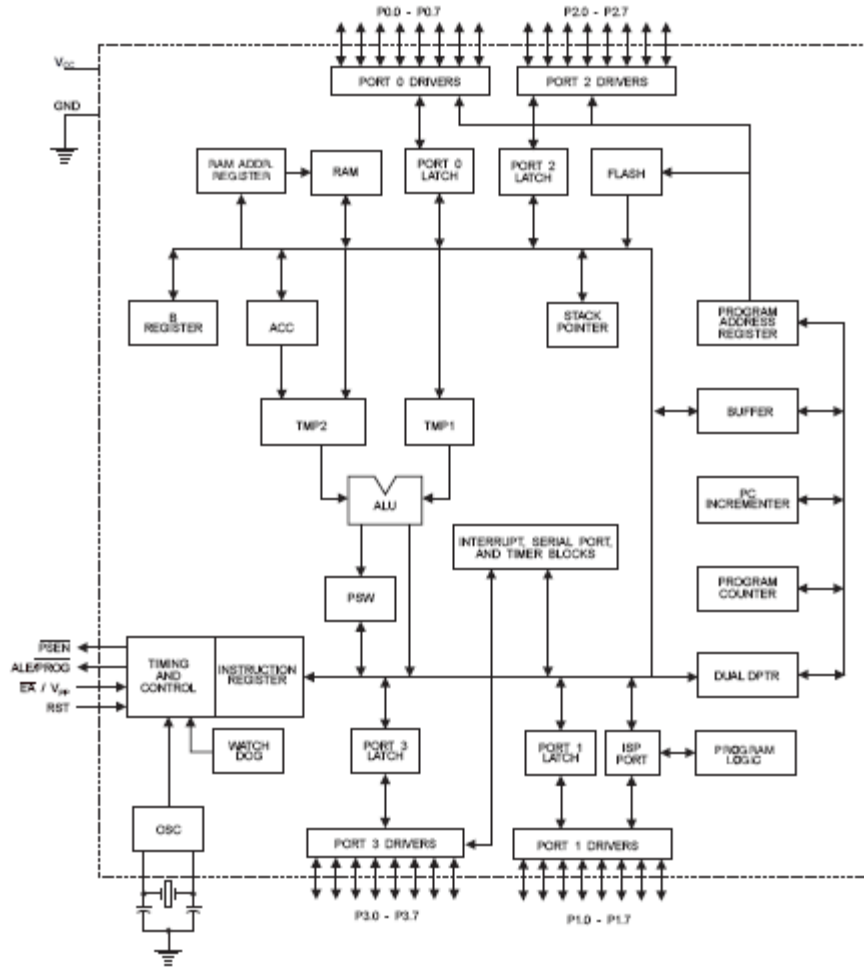


Pin Configurations



AT89S51

Block Diagram





Pin Description

VCC	Supply voltage.								
GND	Ground.								
Port 0	<p>Port 0 is an 8-bit open drain bidirectional I/O port. As an output port, each pin can sink eight TTL inputs. When 1s are written to port 0 pins, the pins can be used as high-impedance inputs.</p> <p>Port 0 can also be configured to be the multiplexed low-order address/data bus during accesses to external program and data memory. In this mode, P0 has internal pull-ups.</p> <p>Port 0 also receives the code bytes during Flash programming and outputs the code bytes during program verification. External pull-ups are required during program verification.</p>								
Port 1	<p>Port 1 is an 8-bit bidirectional I/O port with internal pull-ups. The Port 1 output buffers can sink/source four TTL inputs. When 1s are written to Port 1 pins, they are pulled high by the internal pull-ups and can be used as inputs. As inputs, Port 1 pins that are externally being pulled low will source current (I_{IL}) because of the internal pull-ups.</p> <p>Port 1 also receives the low-order address bytes during Flash programming and verification.</p> <table border="1"><thead><tr><th>Port Pin</th><th>Alternate Functions</th></tr></thead><tbody><tr><td>P1.5</td><td>MOSI (used for In-System Programming)</td></tr><tr><td>P1.6</td><td>MISO (used for In-System Programming)</td></tr><tr><td>P1.7</td><td>SCK (used for In-System Programming)</td></tr></tbody></table>	Port Pin	Alternate Functions	P1.5	MOSI (used for In-System Programming)	P1.6	MISO (used for In-System Programming)	P1.7	SCK (used for In-System Programming)
Port Pin	Alternate Functions								
P1.5	MOSI (used for In-System Programming)								
P1.6	MISO (used for In-System Programming)								
P1.7	SCK (used for In-System Programming)								
Port 2	<p>Port 2 is an 8-bit bidirectional I/O port with internal pull-ups. The Port 2 output buffers can sink/source four TTL inputs. When 1s are written to Port 2 pins, they are pulled high by the internal pull-ups and can be used as inputs. As inputs, Port 2 pins that are externally being pulled low will source current (I_{IL}) because of the internal pull-ups.</p> <p>Port 2 emits the high-order address byte during fetches from external program memory and during accesses to external data memory that use 16-bit addresses (MOVX @ DPTR). In this application, Port 2 uses strong internal pull-ups when emitting 1s. During accesses to external data memory that use 8-bit addresses (MOVX @ R1), Port 2 emits the contents of the P2 Special Function Register.</p> <p>Port 2 also receives the high-order address bits and some control signals during Flash programming and verification.</p>								
Port 3	<p>Port 3 is an 8-bit bidirectional I/O port with internal pull-ups. The Port 3 output buffers can sink/source four TTL inputs. When 1s are written to Port 3 pins, they are pulled high by the internal pull-ups and can be used as inputs. As inputs, Port 3 pins that are externally being pulled low will source current (I_{IL}) because of the pull-ups.</p> <p>Port 3 receives some control signals for Flash programming and verification.</p> <p>Port 3 also serves the functions of various special features of the AT89S51, as shown in the following table.</p>								

Port Pin	Alternate Functions
P3.0	RXD (serial input port)
P3.1	TXD (serial output port)
P3.2	$\overline{\text{INT0}}$ (external interrupt 0)
P3.3	$\overline{\text{INT1}}$ (external interrupt 1)
P3.4	T0 (timer 0 external input)
P3.5	T1 (timer 1 external input)
P3.6	$\overline{\text{WR}}$ (external data memory write strobe)
P3.7	$\overline{\text{RD}}$ (external data memory read strobe)

RST Reset Input. A high on this pin for two machine cycles while the oscillator is running resets the device. This pin drives High for 96 oscillator periods after the Watchdog times out. The DISRTO bit in SFR AUXR (address 8EH) can be used to disable this feature. In the default state of bit DISRTO, the RESET HIGH out feature is enabled.

ALE/ $\overline{\text{PROG}}$ Address Latch Enable (ALE) is an output pulse for latching the low byte of the address during accesses to external memory. This pin is also the program pulse input ($\overline{\text{PROG}}$) during Flash programming.

In normal operation, ALE is emitted at a constant rate of 1/6 the oscillator frequency and may be used for external timing or clocking purposes. Note, however, that one ALE pulse is skipped during each access to external data memory.

If desired, ALE operation can be disabled by setting bit 0 of SFR location 8EH. With the bit set, ALE is active only during a MOVX or MOVC instruction. Otherwise, the pin is weakly pulled high. Setting the ALE-disable bit has no effect if the microcontroller is in external execution mode.

$\overline{\text{PSEN}}$ Program Store Enable ($\overline{\text{PSEN}}$) is the read strobe to external program memory.

When the AT89S51 is executing code from external program memory, $\overline{\text{PSEN}}$ is activated twice each machine cycle, except that two $\overline{\text{PSEN}}$ activations are skipped during each access to external data memory.

$\overline{\text{EA}}/\text{VPP}$ External Access Enable. $\overline{\text{EA}}$ must be strapped to GND in order to enable the device to fetch code from external program memory locations starting at 0000H up to FFFFH. Note, however, that if lock bit 1 is programmed, $\overline{\text{EA}}$ will be internally latched on reset.

$\overline{\text{EA}}$ should be strapped to V_{CC} for internal program executions.

This pin also receives the 12-volt programming enable voltage (V_{PP}) during Flash programming.

XTAL1 Input to the inverting oscillator amplifier and input to the internal clock operating circuit.

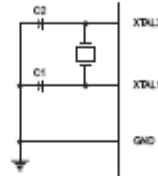
XTAL2 Output from the inverting oscillator amplifier



Oscillator Characteristics

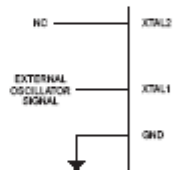
XTAL1 and XTAL2 are the input and output, respectively, of an inverting amplifier that can be configured for use as an on-chip oscillator, as shown in Figure 2. Either a quartz crystal or ceramic resonator may be used. To drive the device from an external clock source, XTAL2 should be left unconnected while XTAL1 is driven, as shown in Figure 3. There are no requirements on the duty cycle of the external clock signal, since the input to the internal clocking circuitry is through a divide-by-two flip-flop, but minimum and maximum voltage high and low time specifications must be observed.

Figure 2. Oscillator Connections



Note: C1, C2 = 30 pF ± 10 pF for Crystals = 40 pF ± 10 pF for Ceramic Resonators

Figure 3. External Clock Drive Configuration



Idle Mode

In Idle mode, the CPU puts itself to sleep while all the on-chip peripherals remain active. The mode is invoked by software. The content of the on-chip RAM and all the special function registers remain unchanged during this mode. The Idle mode can be terminated by any enabled interrupt or by a hardware reset.

Note that when Idle mode is terminated by a hardware reset, the device normally resumes program execution from where it left off, up to two machine cycles before the internal reset algorithm takes control. On-chip hardware inhibits access to internal RAM in this event, but access to the port pins is not inhibited. To eliminate the possibility of an unexpected write to a port pin when Idle mode is terminated by a reset, the instruction following the one that invokes Idle mode should not write to a port pin or to external memory.

Power-down Mode

In the Power-down mode, the oscillator is stopped, and the instruction that invokes Power-down is the last instruction executed. The on-chip RAM and Special Function Registers retain their values until the Power-down mode is terminated. Exit from Power-down mode can be initiated either by a hardware reset or by activation of an enabled external interrupt into INT0 or INT1. Reset redefines the SFRs but does not change the on-chip RAM. The reset should not be activated before V_{DD} is restored to its normal operating level and must be held active long enough to allow the oscillator to restart and stabilize.



Table 5. Status of External Pins During Idle and Power-down Modes

Mode	Program Memory	ALE	PSEN	PORT0	PORT1	PORT2	PORT3
Idle	Internal	1	1	Data	Data	Data	Data
Idle	External	1	1	Float	Data	Address	Data
Power-down	Internal	0	0	Data	Data	Data	Data
Power-down	External	0	0	Float	Data	Data	Data

Program Memory Lock Bits

The AT89S51 has three lock bits that can be left unprogrammed (U) or can be programmed (P) to obtain the additional features listed in the following table.

Table 6. Lock Bit Protection Modes

	Program Lock Bits			Protection Type
	LB1	LB2	LB3	
1	U	U	U	No program lock features
2	P	U	U	MOV _C instructions executed from external program memory are disabled from fetching code bytes from internal memory, EA is sampled and latched on reset, and further programming of the Flash memory is disabled
3	P	P	U	Same as mode 2, but verify is also disabled
4	P	P	P	Same as mode 3, but external execution is also disabled

When lock bit 1 is programmed, the logic level at the EA pin is sampled and latched during reset. If the device is powered up without a reset, the latch initializes to a random value and holds that value until reset is activated. The latched value of EA must agree with the current logic level at that pin in order for the device to function properly.

Programming the Flash – Parallel Mode

The AT89S51 is shipped with the on-chip Flash memory array ready to be programmed. The programming interface needs a high-voltage (12-volt) program enable signal and is compatible with conventional third-party Flash or EPROM programmers.

The AT89S51 code memory array is programmed byte-by-byte.

Programming Algorithm: Before programming the AT89S51, the address, data, and control signals should be set up according to the Flash programming mode table and Figures 13 and 14. To program the AT89S51, take the following steps:

1. Input the desired memory location on the address lines.
2. Input the appropriate data byte on the data lines.
3. Activate the correct combination of control signals.
4. Raise EA/V_{PP} to 12V.
5. Pulse ALE/PROG once to program a byte in the Flash array or the lock bits. The byte-write cycle is self-timed and typically takes no more than 50 μs. Repeat steps 1 through 5, changing the address and data for the entire array or until the end of the object file is reached.

Data Polling: The AT89S51 features Data Polling to indicate the end of a byte write cycle. During a write cycle, an attempted read of the last byte written will result in the complement of the written data on P0.7. Once the write cycle has been completed, true data is valid on all outputs, and the next cycle may begin. Data Polling may begin any time after a write cycle has been initiated.

Ready/Busy: The progress of byte programming can also be monitored by the $\overline{\text{RDY}}/\overline{\text{BSY}}$ output signal. P3.0 is pulled low after ALE goes high during programming to indicate **BSY**. P3.0 is pulled high again when programming is done to indicate **READY**.

Program Verify: If lock bits LB1 and LB2 have not been programmed, the programmed code data can be read back via the address and data lines for verification. The status of the individual lock bits can be verified directly by reading them back.

Reading the Signature Bytes: The signature bytes are read by the same procedure as a normal verification of locations 000H, 100H, and 200H, except that P3.6 and P3.7 must be pulled to a logic low. The values returned are as follows.

(000H) = 1EH indicates manufactured by Atmel
 (100H) = 51H indicates 89S51
 (200H) = 06H

Chip Erase: In the parallel programming mode, a chip erase operation is initiated by using the proper combination of control signals and by pulsing ALE/ $\overline{\text{PROG}}$ low for a duration of 200 ns - 500 ns.

In the serial programming mode, a chip erase operation is initiated by issuing the Chip Erase instruction. In this mode, chip erase is self-timed and takes about 500 ms.

During chip erase, a serial read from any address location will return 00H at the data output.

Programming the Flash – Serial Mode

The Code memory array can be programmed using the serial ISP interface while RST is pulled to V_{CC} . The serial interface consists of pins SCK, MOSI (Input) and MISO (output). After RST is set high, the Programming Enable instruction needs to be executed first before other operations can be executed. Before a reprogramming sequence can occur, a Chip Erase operation is required.

The Chip Erase operation turns the content of every memory location in the Code array into FFH.

Either an external system clock can be supplied at pin XTAL1 or a crystal needs to be connected across pins XTAL1 and XTAL2. The maximum serial clock (SCK) frequency should be less than 1/16 of the crystal frequency. With a 33 MHz oscillator clock, the maximum SCK frequency is 2 MHz.

Serial Programming Algorithm

To program and verify the AT89S51 in the serial programming mode, the following sequence is recommended:

1. Power-up sequence:
 Apply power between VCC and GND pins.
 Set RST pin to "H".
 If a crystal is not connected across pins XTAL1 and XTAL2, apply a 3 MHz to 33 MHz clock to XTAL1 pin and wait for at least 10 milliseconds.
2. Enable serial programming by sending the Programming Enable serial instruction to pin MOSI/P1.5. The frequency of the shift clock supplied at pin SCK/P1.7 needs to be less than the CPU clock at XTAL1 divided by 16.
3. The Code array is programmed one byte at a time in either the Byte or Page mode. The write cycle is self-timed and typically takes less than 0.5 ms at 5V.
4. Any memory location can be verified by using the Read instruction that returns the content at the selected address at serial output MISO/P1.6.
5. At the end of a programming session, RST can be set low to commence normal device operation.





Power-off sequence (if needed):
 Set XTAL1 to "L" (if a crystal is not used).
 Set RST to "L".
 Turn V_{CC} power off.

Data Polling: The Data Polling feature is also available in the serial mode. In this mode, during a write cycle an attempted read of the last byte written will result in the complement of the MSB of the serial output byte on MISO.

Serial Programming Instruction Set

The Instruction Set for Serial Programming follows a 4-byte protocol and is shown in Table 8 on page 18.

Programming Interface – Parallel Mode

Every code byte in the Flash array can be programmed by using the appropriate combination of control signals. The write operation cycle is self-timed and once initiated, will automatically time itself to completion.

All major programming vendors offer worldwide support for the Atmel microcontroller series. Please contact your local programming vendor for the appropriate software revision.

Table 7. Flash Programming Modes

Mode	V_{CC}	RST	PSEN	ALE/ PROG	EA/ V_{PP}	P2.6	P2.7	P3.3	P3.6	P3.7	P0.7-0 Data	P2.3-6 P1.7-0 Address	
												A11-8	A7-0
Write Code Data	5V	H	L		12V	L	H	H	H	H	D_w	A11-8	A7-0
Read Code Data	5V	H	L	H	H	L	L	L	H	H	D_{out}	A11-8	A7-0
Write Lock Bit 1	5V	H	L		12V	H	H	H	H	H	X	X	X
Write Lock Bit 2	5V	H	L		12V	H	H	H	L	L	X	X	X
Write Lock Bit 3	5V	H	L		12V	H	L	H	H	L	X	X	X
Read Lock Bits 1, 2, 3	5V	H	L	H	H	H	H	L	H	L	P0.2 P0.3 P0.4	X	X
Chip Erase	5V	H	L		12V	H	L	H	L	L	X	X	X
Read Atmel ID	5V	H	L	H	H	L	L	L	L	L	1EH	0000	00H
Read Device ID	5V	H	L	H	H	L	L	L	L	L	51H	0001	00H
Read Device ID	5V	H	L	H	H	L	L	L	L	L	06H	0010	00H

- Notes:
1. Each PROG pulse is 200 ns - 500 ns for Chip Erase.
 2. Each PROG pulse is 200 ns - 500 ns for Write Code Data.
 3. Each PROG pulse is 200 ns - 500 ns for Write Lock Bits.
 4. RDY/BSY signal is output on P3.0 during programming.
 5. X = don't care.

Figure 4. Programming the Flash Memory (Parallel Mode)

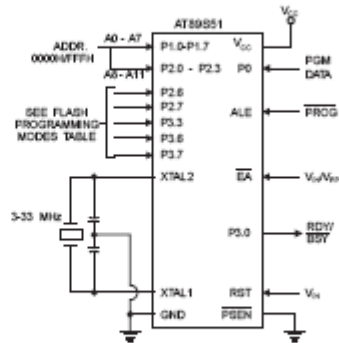
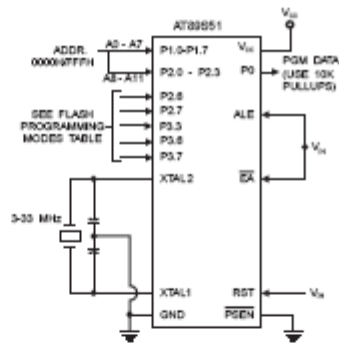


Figure 5. Verifying the Flash Memory (Parallel Mode)





Flash Programming and Verification Characteristics (Parallel Mode)

$T_A = 20^\circ\text{C to } 30^\circ\text{C}$, $V_{CC} = 4.5 \text{ to } 5.5\text{V}$

Symbol	Parameter	Min	Max	Units
V_{PP}	Programming Supply Voltage	11.5	12.5	V
I_{PP}	Programming Supply Current		10	mA
I_{CC}	V_{CC} Supply Current		30	mA
$1/f_{CLOCK}$	Oscillator Frequency	3	33	MHz
t_{AVSL}	Address Setup to $\overline{\text{PROG}}$ Low	$48t_{CLOCK}$		
t_{AHUX}	Address Hold After $\overline{\text{PROG}}$	$48t_{CLOCK}$		
t_{DVAL}	Data Setup to $\overline{\text{PROG}}$ Low	$48t_{CLOCK}$		
t_{DHOX}	Data Hold After $\overline{\text{PROG}}$	$48t_{CLOCK}$		
t_{ENSH}	P2.7 ($\overline{\text{ENABLE}}$) High to V_{PP}	$48t_{CLOCK}$		
t_{VPSL}	V_{PP} Setup to $\overline{\text{PROG}}$ Low	10		μs
t_{VPHL}	V_{PP} Hold After $\overline{\text{PROG}}$	10		μs
t_{OLWH}	$\overline{\text{PROG}}$ Width	0.2	1	μs
t_{WADV}	Address to Data Valid		$48t_{CLOCK}$	
t_{ELOW}	$\overline{\text{ENABLE}}$ Low to Data Valid		$48t_{CLOCK}$	
t_{DFHZ}	Data Float After $\overline{\text{ENABLE}}$	0	$48t_{CLOCK}$	
t_{PHSL}	$\overline{\text{PROG}}$ High to $\overline{\text{BUSY}}$ Low		1.0	μs
t_{WC}	Byte Write Cycle Time		60	μs

Figure 6. Flash Programming and Verification Waveforms – Parallel Mode

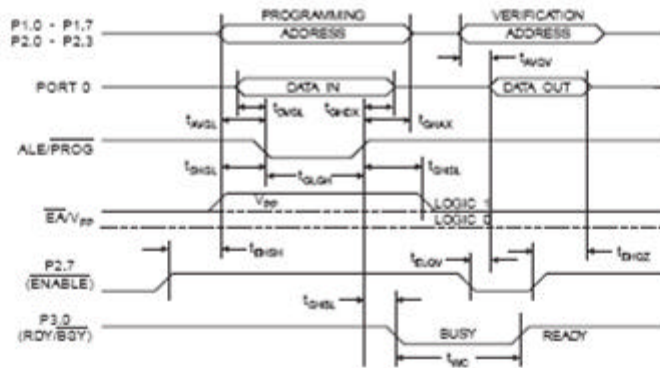
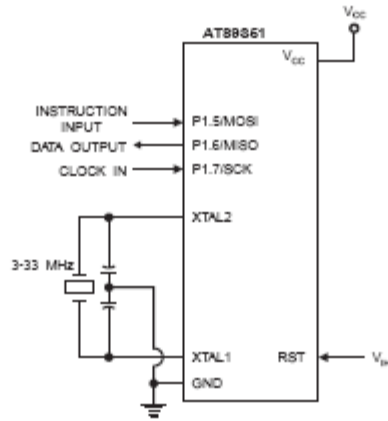


Figure 7. Flash Memory Serial Downloading



Flash Programming and Verification Waveforms – Serial Mode

Figure 8. Serial Programming Waveforms

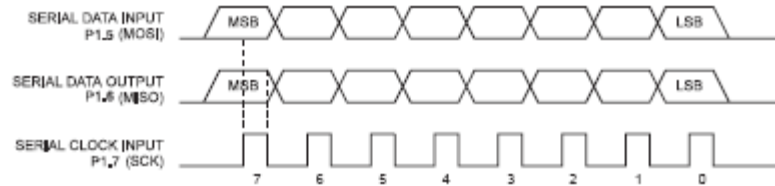




Table 8. Serial Programming Instruction Set

Instruction	Instruction Format				Operation
	Byte 1	Byte 2	Byte 3	Byte 4	
Programming Enable	1010 1100	0101 0011	xxxx xxxx	xxxx xxxx 0110 1001 (Output)	Enable Serial Programming while RST is high
Chip Erase	1010 1100	100x xxxx	xxxx xxxx	xxxx xxxx	Chip Erase Flash memory array
Read Program Memory (Byte Mode)	0010 0000	xxxx			Read data from Program memory in the byte mode
Write Program Memory (Byte Mode)	0100 0000	xxxx			Write data to Program memory in the byte mode
Write Lock Bits ⁽²⁾	1010 1100	1110 00	xxxx xxxx	xxxx xxxx	Write Lock bits. See Note (2).
Read Lock Bits	0010 0100	xxxx xxxx	xxxx xxxx	xx	Read back current status of the lock bits (a programmed lock bit reads back as a "1")
Read Signature Bytes ⁽¹⁾	0010 1000	xxx		Signature Byte	Read Signature Byte
Read Program Memory (Page Mode)	0011 0000	xxxx	Byte 0	Byte 1... Byte 255	Read data from Program memory in the Page Mode (256 bytes)
Write Program Memory (Page Mode)	0101 0000	xxxx	Byte 0	Byte 1... Byte 255	Write data to Program memory in the Page Mode (256 bytes)

Notes: 1. The signature bytes are not readable in Lock Bit Modes 3 and 4.

- 2. B1 = 0, B2 = 0 → Mode 1, no lock protection
- B1 = 0, B2 = 1 → Mode 2, lock bit 1 activated
- B1 = 1, B2 = 0 → Mode 3, lock bit 2 activated
- B1 = 1, B2 = 1 → Mode 4, lock bit 3 activated

Each of the lock bits needs to be activated sequentially before Mode 4 can be executed.

After Reset signal is high, SCK should be low for at least 64 system clocks before it goes high to clock in the enable data bytes. No pulsing of Reset signal is necessary. SCK should be no faster than 1/16 of the system clock at XTAL1.

For Page Read/Write, the data always starts from byte 0 to 255. After the command byte and upper address byte are latched, each byte thereafter is treated as data until all 256 bytes are shifted in/out. Then the next instruction will be ready to be decoded.



Table 8. Serial Programming Instruction Set

Instruction	Instruction Format				Operation
	Byte 1	Byte 2	Byte 3	Byte 4	
Programming Enable	1010 1100	0101 0011	xxxx xxxx	xxxx xxxx 0110 1001 (Output)	Enable Serial Programming while RST is high
Chip Erase	1010 1100	100x xxxx	xxxx xxxx	xxxx xxxx	Chip Erase Flash memory array
Read Program Memory (Byte Mode)	0010 0000	xxxx			Read data from Program memory in the byte mode
Write Program Memory (Byte Mode)	0100 0000	xxxx			Write data to Program memory in the byte mode
Write Lock Bits ⁽²⁾	1010 1100	1110 00	xxxx xxxx	xxxx xxxx	Write Lock bits. See Note (2).
Read Lock Bits	0010 0100	xxxx xxxx	xxxx xxxx	xx	Read back current status of the lock bits (a programmed lock bit reads back as a "1")
Read Signature Bytes ⁽¹⁾	0010 1000	xxx		Signature Byte	Read Signature Byte
Read Program Memory (Page Mode)	0011 0000	xxxx	Byte 0	Byte 1... Byte 255	Read data from Program memory in the Page Mode (256 bytes)
Write Program Memory (Page Mode)	0101 0000	xxxx	Byte 0	Byte 1... Byte 255	Write data to Program memory in the Page Mode (256 bytes)

Notes: 1. The signature bytes are not readable in Lock Bit Modes 3 and 4.

- 2. B1 = 0, B2 = 0 → Mode 1, no lock protection
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- B1 = 1, B2 = 0 → Mode 3, lock bit 2 activated
- B1 = 1, B2 = 1 → Mode 4, lock bit 3 activated

Each of the lock bits needs to be activated sequentially before Mode 4 can be executed.

After Reset signal is high, SCK should be low for at least 64 system clocks before it goes high to clock in the enable data bytes. No pulsing of Reset signal is necessary. SCK should be no faster than 1/16 of the system clock at XTAL1.

For Page Read/Write, the data always starts from byte 0 to 255. After the command byte and upper address byte are latched, each byte thereafter is treated as data until all 256 bytes are shifted in/out. Then the next instruction will be ready to be decoded.

Serial Programming Characteristics

Figure 9. Serial Programming Timing

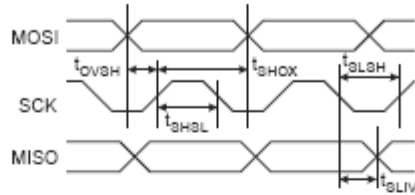


Table 9. Serial Programming Characteristics, $T_A = -40^\circ\text{C}$ to 85°C , $V_{CC} = 4.0 - 5.5\text{V}$ (Unless Otherwise Noted)

Symbol	Parameter	Min	Typ	Max	Units
f_{CLCKL}	Oscillator Frequency	0		33	MHz
t_{CLCKL}	Oscillator Period	30			ns
t_{SHHL}	SCK Pulse Width High	$8 t_{\text{CLCKL}}$			ns
t_{SLHL}	SCK Pulse Width Low	$8 t_{\text{CLCKL}}$			ns
t_{OVSH}	MOSI Setup to SCK High	t_{CLCKL}			ns
t_{SHOH}	MOSI Hold after SCK High	$2 t_{\text{CLCKL}}$			ns
t_{SLIV}	SCK Low to MISO Valid	10	16	32	ns
t_{ERASE}	Chip Erase Instruction Cycle Time			500	ms
t_{BWC}	Serial Byte Write Cycle Time			$64 t_{\text{CLCKL}} + 400$	μs





Absolute Maximum Ratings*

Operating Temperature.....	-55°C to +125°C
Storage Temperature.....	-65°C to +150°C
Voltage on Any Pin with Respect to Ground.....	-1.0V to +7.0V
Maximum Operating Voltage.....	5.5V
DC Output Current.....	15.0 mA

*NOTICE: Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

DC Characteristics

The values shown in this table are valid for $T_A = -40^\circ\text{C}$ to 85°C and $V_{CC} = 4.0\text{V}$ to 5.5V , unless otherwise noted.

Symbol	Parameter	Condition	Min	Max	Units
V_{IL}	Input Low Voltage	(Except \overline{EA})	-0.5	$0.2 V_{CC} - 0.1$	V
V_{IL1}	Input Low Voltage (\overline{EA})		-0.5	$0.2 V_{CC} - 0.3$	V
V_{IH}	Input High Voltage	(Except XTAL1, RST)	$0.2 V_{CC} + 0.9$	$V_{CC} + 0.5$	V
V_{IH1}	Input High Voltage	(XTAL1, RST)	$0.7 V_{CC}$	$V_{CC} + 0.5$	V
V_{OL}	Output Low Voltage ⁽¹⁾ (Ports 1,2,3)	$I_{OL} = 1.6\text{ mA}$		0.45	V
V_{OL1}	Output Low Voltage ⁽¹⁾ (Port 0, ALE, PSEN)	$I_{OL} = 3.2\text{ mA}$		0.45	V
V_{OH}	Output High Voltage (Ports 1,2,3, ALE, PSEN)	$I_{OH} = -60\ \mu\text{A}$, $V_{CC} = 5\text{V} \pm 10\%$	2.4		V
		$I_{OH} = -25\ \mu\text{A}$	$0.75 V_{CC}$		V
		$I_{OH} = -10\ \mu\text{A}$	$0.9 V_{CC}$		V
V_{OH1}	Output High Voltage (Port 0 in External Bus Mode)	$I_{OH} = -800\ \mu\text{A}$, $V_{CC} = 5\text{V} \pm 10\%$	2.4		V
		$I_{OH} = -300\ \mu\text{A}$	$0.75 V_{CC}$		V
		$I_{OH} = -80\ \mu\text{A}$	$0.9 V_{CC}$		V
I_{Lk}	Logical 0 Input Current (Ports 1,2,3)	$V_{IN} = 0.45\text{V}$		-50	μA
I_{TL}	Logical 1 to 0 Transition Current (Ports 1,2,3)	$V_{IN} = 2\text{V}$, $V_{CC} = 5\text{V} \pm 10\%$		-650	μA
I_{LI}	Input Leakage Current (Port 0, \overline{EA})	$0.45 < V_{IN} < V_{CC}$		± 10	μA
RRST	Reset Pulldown Resistor		50	300	$\text{K}\Omega$
C_{IO}	Pin Capacitance	Test Freq. = 1 MHz, $T_A = 25^\circ\text{C}$		10	pF
I_{CC}	Power Supply Current	Active Mode, 12 MHz		25	mA
		Idle Mode, 12 MHz		6.5	mA
		Power-down Mode ⁽²⁾	$V_{CC} = 5.5\text{V}$	50	μA

- Notes: 1. Under steady state (non-transient) conditions, I_{OL} must be externally limited as follows:
 Maximum I_{OL} per port pin: 10 mA
 Maximum I_{OL} per 8-bit port:
 Port 0: 26 mA Ports 1, 2, 3: 15 mA
 Maximum total I_{OL} for all output pins: 71 mA
 If I_{OL} exceeds the test condition, V_{OL} may exceed the related specification. Pins are not guaranteed to sink current greater than the listed test conditions.
2. Minimum V_{CC} for Power-down is 2V.

AT89S51

2487A-1001

AC Characteristics

Under operating conditions, load capacitance for Port 0, ALE/ $\overline{\text{PROG}}$, and $\overline{\text{PSEN}}$ = 100 pF; load capacitance for all other outputs = 80 pF.

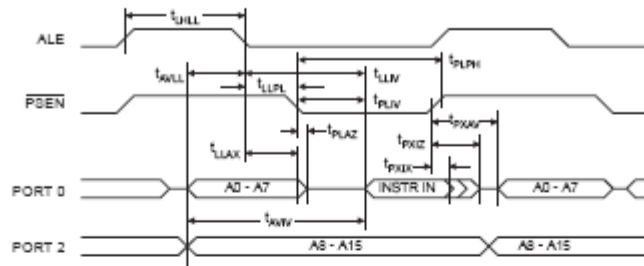
External Program and Data Memory Characteristics

Symbol	Parameter	12 MHz Oscillator		Variable Oscillator		Units
		Min	Max	Min	Max	
$1/f_{\text{OCLCL}}$	Oscillator Frequency			0	33	MHz
t_{LHLL}	ALE Pulse Width	127		$2t_{\text{OCLCL}}-40$		ns
t_{WLL}	Address Valid to ALE Low	43		$t_{\text{OCLCL}}-25$		ns
t_{LHAX}	Address Hold After ALE Low	48		$t_{\text{OCLCL}}-25$		ns
t_{LLIV}	ALE Low to Valid Instruction In		233		$4t_{\text{OCLCL}}-65$	ns
t_{LLPL}	ALE Low to $\overline{\text{PSEN}}$ Low	43		$t_{\text{OCLCL}}-25$		ns
t_{PLPH}	$\overline{\text{PSEN}}$ Pulse Width	205		$3t_{\text{OCLCL}}-45$		ns
t_{PLIV}	$\overline{\text{PSEN}}$ Low to Valid Instruction In		145		$3t_{\text{OCLCL}}-60$	ns
t_{PXIX}	Input Instruction Hold After $\overline{\text{PSEN}}$	0		0		ns
t_{PXIZ}	Input Instruction Float After $\overline{\text{PSEN}}$		59		$t_{\text{OCLCL}}-25$	ns
t_{PXIV}	$\overline{\text{PSEN}}$ to Address Valid	75		$t_{\text{OCLCL}}-5$		ns
t_{WIV}	Address to Valid Instruction In		312		$5t_{\text{OCLCL}}-80$	ns
t_{PLAZ}	$\overline{\text{PSEN}}$ Low to Address Float		10		10	ns
t_{RLRH}	$\overline{\text{RD}}$ Pulse Width	400		$5t_{\text{OCLCL}}-100$		ns
t_{RWLH}	$\overline{\text{WR}}$ Pulse Width	400		$5t_{\text{OCLCL}}-100$		ns
t_{RLDV}	$\overline{\text{RD}}$ Low to Valid Data In		252		$5t_{\text{OCLCL}}-90$	ns
t_{RHDX}	Data Hold After $\overline{\text{RD}}$	0		0		ns
t_{RHIZ}	Data Float After $\overline{\text{RD}}$		97		$2t_{\text{OCLCL}}-28$	ns
t_{LLDV}	ALE Low to Valid Data In		517		$8t_{\text{OCLCL}}-150$	ns
t_{WLDV}	Address to Valid Data In		585		$9t_{\text{OCLCL}}-165$	ns
t_{LWLL}	ALE Low to $\overline{\text{RD}}$ or $\overline{\text{WR}}$ Low	200	300	$3t_{\text{OCLCL}}-50$	$3t_{\text{OCLCL}}+50$	ns
t_{WVLL}	Address to $\overline{\text{RD}}$ or $\overline{\text{WR}}$ Low	203		$4t_{\text{OCLCL}}-75$		ns
t_{QVWX}	Data Valid to $\overline{\text{WR}}$ Transition	23		$t_{\text{OCLCL}}-30$		ns
t_{QVWH}	Data Valid to $\overline{\text{WR}}$ High	433		$7t_{\text{OCLCL}}-130$		ns
t_{WHDX}	Data Hold After $\overline{\text{WR}}$	33		$t_{\text{OCLCL}}-25$		ns
t_{RLAZ}	$\overline{\text{RD}}$ Low to Address Float		0		0	ns
t_{WHIH}	$\overline{\text{RD}}$ or $\overline{\text{WR}}$ High to ALE High	43	123	$t_{\text{OCLCL}}-25$	$t_{\text{OCLCL}}+25$	ns

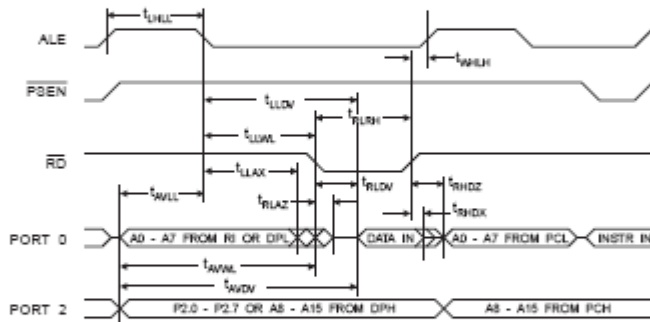




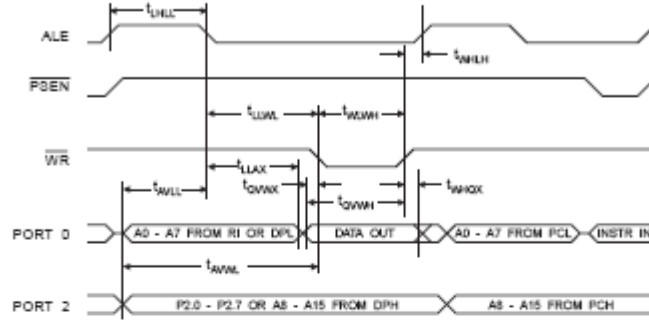
External Program Memory Read Cycle



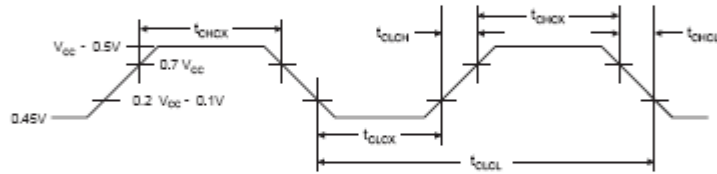
External Data Memory Read Cycle



External Data Memory Write Cycle



External Clock Drive Waveforms



External Clock Drive

Symbol	Parameter	Min	Max	Units
$1/t_{CLCL}$	Oscillator Frequency	0	33	MHz
t_{CLCL}	Clock Period	30		ns
t_{CHCX}	High Time	12		ns
t_{CLCX}	Low Time	12		ns
t_{CLCH}	Rise Time		5	ns
t_{CHCL}	Fall Time		5	ns



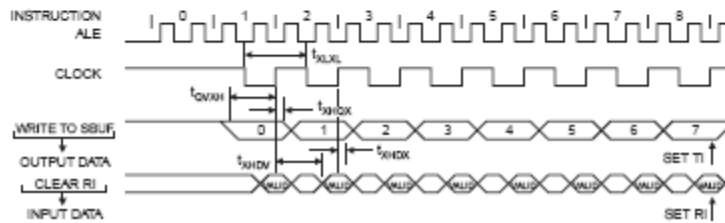


Serial Port Timing: Shift Register Mode Test Conditions

The values in this table are valid for $V_{CC} = 4.0V$ to $5.5V$ and Load Capacitance = 80 pF.

Symbol	Parameter	12 MHz Osc		Variable Oscillator		Units
		Min	Max	Min	Max	
t_{CLK}	Serial Port Clock Cycle Time	1.0		$12t_{CLK}$		μs
t_{QVH}	Output Data Setup to Clock Rising Edge	700		$10t_{CLK}-133$		ns
t_{QVX}	Output Data Hold After Clock Rising Edge	50		$2t_{CLK}-80$		ns
t_{HDX}	Input Data Hold After Clock Rising Edge	0		0		ns
t_{HIV}	Clock Rising Edge to Input Data Valid		700		$10t_{CLK}-133$	ns

Shift Register Mode Timing Waveforms



AC Testing Input/Output Waveforms⁽¹⁾



Note: 1. AC Inputs during testing are driven at $V_{CC} - 0.5V$ for a logic 1 and $0.45V$ for a logic 0. Timing measurements are made at V_{IH} min. for a logic 1 and V_{IL} max. for a logic 0.

Float Waveforms⁽¹⁾



Note: 1. For timing purposes, a port pin is no longer floating when a 100 mV change from load voltage occurs. A port pin begins to float when a 100 mV change from the loaded V_{OH}/V_{OL} level occurs.

Ordering Information

Speed (MHz)	Power Supply	Ordering Code	Package	Operation Range
24	4.0V to 5.5V	AT89S51-24AC	44A	Commercial (0°C to 70°C)
		AT89S51-24JC	44J	
		AT89S51-24PC	40P6	
		AT89S51-24AI	44A	Industrial (-40°C to 85°C)
		AT89S51-24JI	44J	
		AT89S51-24PI	40P6	
33	4.5V to 5.5V	AT89S51-33AC	44A	Commercial (0°C to 70°C)
		AT89S51-33JC	44J	
		AT89S51-33PC	40P6	

 = Preliminary Availability

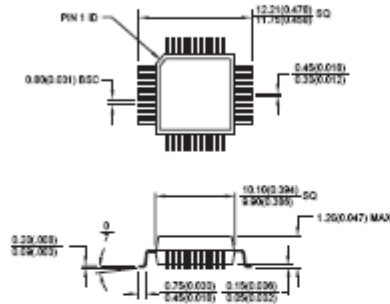
Package Type	
44A	44-lead, Thin Plastic Gull Wing Quad Flatpack (TQFP)
44J	44-lead, Plastic J-leaded Chip Carrier (PLCC)
40P6	40-pin, 0.600" Wide, Plastic Dual In-line Package (PDIP)





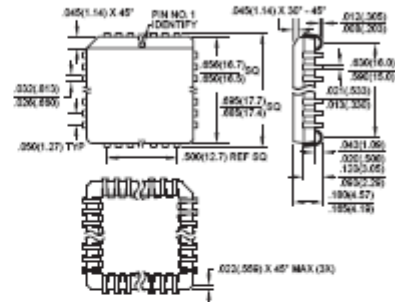
Packaging Information

44A, 44-lead, Thin (1.0 mm) Plastic Gull Wing Quad Flat Package (TQFP)
Dimensions in Millimeters and (Inches)*

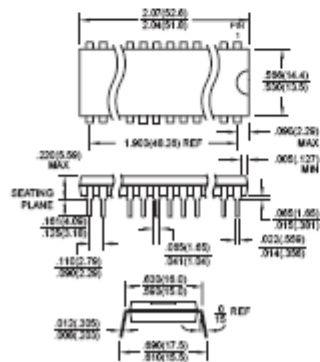


*Controlling dimension: millimeters

44J, 44-lead, Plastic J-leaded Chip Carrier (PLCC)
Dimensions in Inches and (Millimeters)



40PS, 40-pin, 0.600" Wide, Plastic Dual Inline Package (PDIP)
Dimensions in Inches and (Millimeters)
JEDEC STANDARD MS-011 AC



FEATURES

- Low-Sine Wave Distortion, 0.5%, Typical
- Excellent Temperature Stability, 20ppm/°C, Typ.
- Wide Sweep Range, 2000:1, Typical
- Low-Supply Sensitivity, 0.01%V, Typ.
- Linear Amplitude Modulation
- TTL Compatible FSK Controls
- Wide Supply Range, 10V to 26V
- Adjustable Duty Cycle, 1% TO 99%

APPLICATIONS

- Waveform Generation
- Sweep Generation
- AM/FM Generation
- V/F Conversion
- FSK Generation
- Phase-Locked Loops (VCO)

GENERAL DESCRIPTION

The XR-2206 is a monolithic function generator integrated circuit capable of producing high quality sine, square, triangle, ramp, and pulse waveforms of high-stability and accuracy. The output waveforms can be both amplitude and frequency modulated by an external voltage. Frequency of operation can be selected externally over a range of 0.01Hz to more than 1MHz.

The circuit is ideally suited for communications, instrumentation, and function generator applications requiring sinusoidal tone, AM, FM, or FSK generation. It has a typical drift specification of 20ppm/°C. The oscillator frequency can be linearly swept over a 2000:1 frequency range with an external control voltage, while maintaining low distortion.

ORDERING INFORMATION

Part No.	Package	Operating Temperature Range
XR-2206M	16 Lead 300 Mil CDIP	-55°C to +125°C
XR-2206P	16 Lead 300 Mil PDIP	-40°C to +85°C
XR-2206CP	16 Lead 300 Mil PDIP	0°C to +70°C
XR-2206D	16 Lead 300 Mil JEDEC SOIC	0°C to +70°C

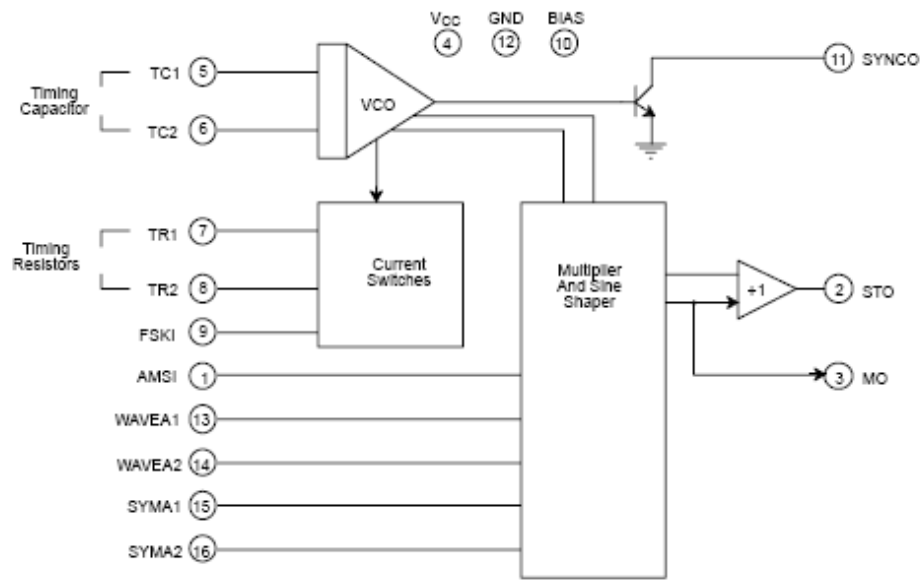
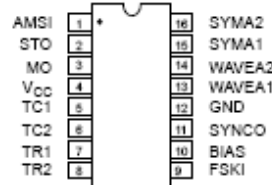
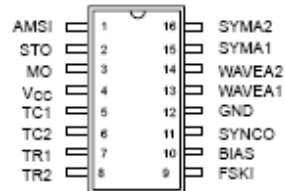


Figure 1. XR-2206 Block Diagram



16 Lead PDIP, CDIP (0.300")



16 Lead SOIC (Jedec, 0.300")

PIN DESCRIPTION

Pin #	Symbol	Type	Description
1	AMSI	I	Amplitude Modulating Signal Input.
2	STO	O	Sine or Triangle Wave Output.
3	MO	O	Multiplier Output.
4	V _{CC}		Positive Power Supply.
5	TC1	I	Timing Capacitor Input.
6	TC2	I	Timing Capacitor Input.
7	TR1	O	Timing Resistor 1 Output.
8	TR2	O	Timing Resistor 2 Output.
9	FSKI	I	Frequency Shift Keying Input.
10	BIAS	O	Internal Voltage Reference.
11	SYNCO	O	Sync Output. This output is a open collector and needs a pull up resistor to V _{CC} .
12	GND		Ground pin.
13	WAVEA1	I	Wave Form Adjust Input 1.
14	WAVEA2	I	Wave Form Adjust Input 2.
15	SYMA1	I	Wave Symetry Adjust 1.
16	SYMA2	I	Wave Symetry Adjust 2.

DC ELECTRICAL CHARACTERISTICS

Test Conditions: Test Circuit of Figure 2 $V_{CC} = 12V$, $T_A = 25^\circ C$, $C = 0.01\mu F$, $R_1 = 100k\Omega$, $R_2 = 10k\Omega$, $R_3 = 25k\Omega$
 Unless Otherwise Specified. S_1 open for triangle, closed for sine wave.

Parameters	XR-2206MP			XR-2206CP/D			Units	Conditions
	Min.	Typ.	Max.	Min.	Typ.	Max.		
General Characteristics								
Single Supply Voltage	10		26	10		26	V	
Split-Supply Voltage	± 5		± 13	± 5		± 13	V	
Supply Current		12	17		14	20	mA	$R_1 \geq 10k\Omega$
Oscillator Section								
Max. Operating Frequency	0.5	1		0.5	1		MHz	$C = 1000pF$, $R_1 = 1k\Omega$
Lowest Practical Frequency		0.01			0.01		Hz	$C = 50\mu F$, $R_1 = 2M\Omega$
Frequency Accuracy		± 1	± 4		± 2		% of f_0	$f_0 = 1/R_1C$
Temperature Stability		± 10	± 50		± 20		ppm/ $^\circ C$	$0^\circ C \leq T_A \leq 70^\circ C$
Frequency								$R_1 = R_2 = 20k\Omega$
Sine Wave Amplitude Stability ²		4800			4800		ppm/ $^\circ C$	
Supply Sensitivity		0.01	0.1		0.01		%/V	$V_{LOW} = 10V$, $V_{HIGH} = 20V$, $R_1 = R_2 = 20k\Omega$
Sweep Range	1000:1	2000:1			2000:1		$f_H = f_L$	$f_H @ R_1 = 1k\Omega$ $f_L @ R_1 = 2M\Omega$
Sweep Linearity								
10:1 Sweep		2			2		%	$f_L = 1kHz$, $f_H = 10kHz$
1000:1 Sweep		8			8		%	$f_L = 100Hz$, $f_H = 100kHz$
FM Distortion		0.1			0.1		%	$\pm 10\%$ Deviation
Recommended Timing Components								
Timing Capacitor: C	0.001		100	0.001		100	μF	Figure 5
Timing Resistors: R_1 & R_2	1		2000	1		2000	k Ω	
Triangle Sine Wave Output¹								
Triangle Amplitude		160			160		mV/k Ω	Figure 2, S_1 Open
Sine Wave Amplitude	40	60	80		60		mV/k Ω	Figure 2, S_1 Closed
Max. Output Swing		6			6		Vp-p	
Output Impedance		600			600		Ω	
Triangle Linearity		1			1		%	
Amplitude Stability		0.5			0.5		dB	For 1000:1 Sweep
Sine Wave Distortion								
Without Adjustment		2.5			2.5		%	$R_1 = 30k\Omega$
With Adjustment		0.4	1.0		0.5	1.5	%	See Figure 7 and Figure 8

Notes

¹ Output amplitude is directly proportional to the resistance, R_3 , on Pin 3. See Figure 3.

² For maximum amplitude stability, R_3 should be a positive temperature coefficient resistor.

Bold face parameters are covered by production test and guaranteed over operating temperature range.

DC ELECTRICAL CHARACTERISTICS (CONT'D)

Parameters	XR-2206M/P			XR-2206CP/D			Units	Conditions
	Min.	Typ.	Max.	Min.	Typ.	Max.		
Amplitude Modulation								
Input Impedance	50	100		50	100		kΩ	
Modulation Range		100			100		%	
Carrier Suppression		55			55		dB	
Linearity		2			2		%	For 95% modulation
Square-Wave Output								
Amplitude		12			12		Vp-p	Measured at Pin 11.
Rise Time		250			250		ns	$C_L = 10\text{pF}$
Fall Time		50			50		ns	$C_L = 10\text{pF}$
Saturation Voltage		0.2	0.4		0.2	0.6	V	$I_L = 2\text{mA}$
Leakage Current		0.1	20		0.1	100	μA	$V_{CC} = 28\text{V}$
FSK Keying Level (Pin 9)	0.8	1.4	2.4	0.8	1.4	2.4	V	See section on circuit controls
Reference Bypass Voltage	2.9	3.1	3.3	2.5	3	3.5	V	Measured at Pin 10.

Notes

¹ Output amplitude is directly proportional to the resistance, R_3 , on Pin 3. See Figure 3.

² For maximum amplitude stability, R_3 should be a positive temperature coefficient resistor.

Bold face parameters are covered by production test and guaranteed over operating temperature range.

Specifications are subject to change without notice

ABSOLUTE MAXIMUM RATINGS

Power Supply	28V	Total Timing Current	8mA
Power Dissipation	750mW	Storage Temperature	-85°C to +150°C
Derate Above 25°C	5mW/°C		

SYSTEM DESCRIPTION

The XR-2206 is comprised of four functional blocks; a voltage-controlled oscillator (VCO), an analog multiplier and sine-shaper; a unity gain buffer amplifier; and a set of current switches.

The VCO produces an output frequency proportional to an input current, which is set by a resistor from the timing

terminals to ground. With two timing pins, two discrete output frequencies can be independently produced for FSK generation applications by using the FSK input control pin. This input controls the current switches which select one of the timing resistor currents, and routes it to the VCO.

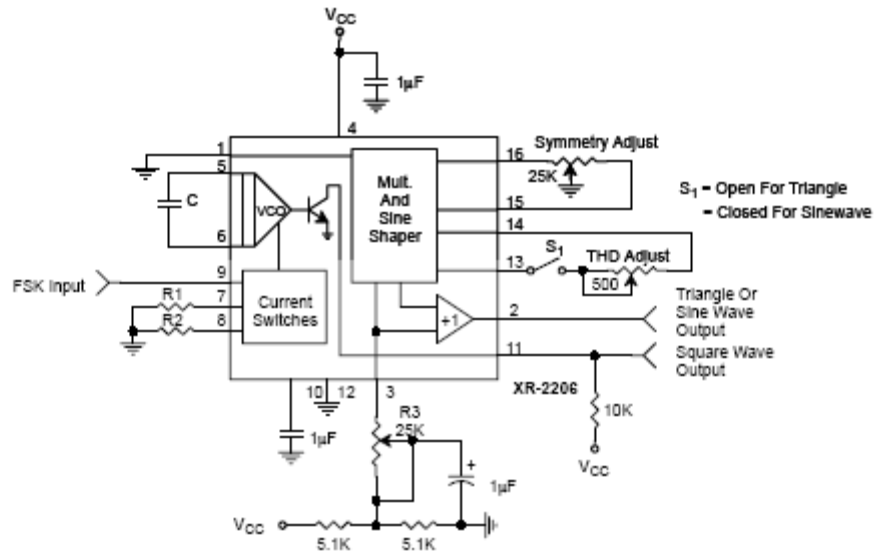


Figure 2. Basic Test Circuit

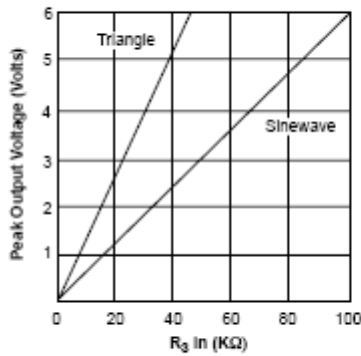


Figure 3. Output Amplitude as a Function of the Resistor, R₃, at Pin 3

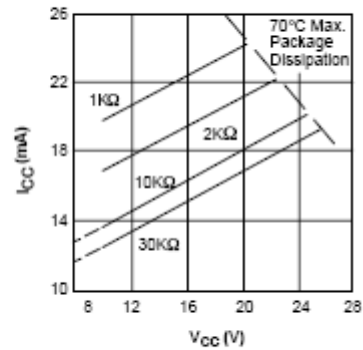


Figure 4. Supply Current vs Supply Voltage, Timing, R

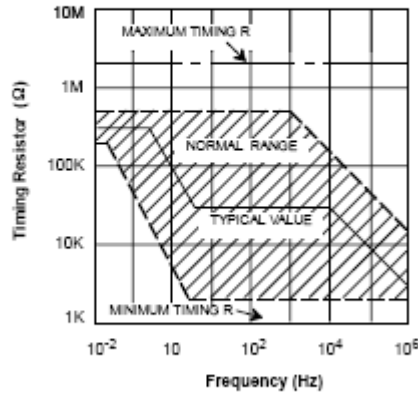


Figure 5. R versus Oscillation Frequency.

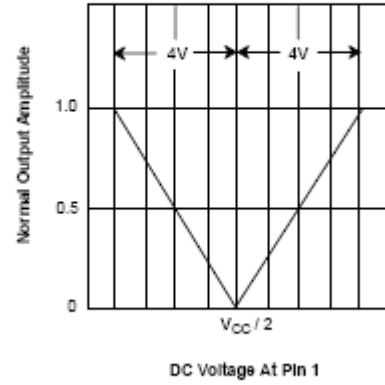


Figure 6. Normalized Output Amplitude versus DC Bias at AM Input (Pin 1)

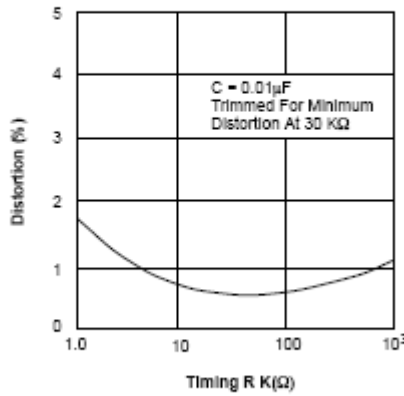


Figure 7. Trimmed Distortion versus Timing Resistor.

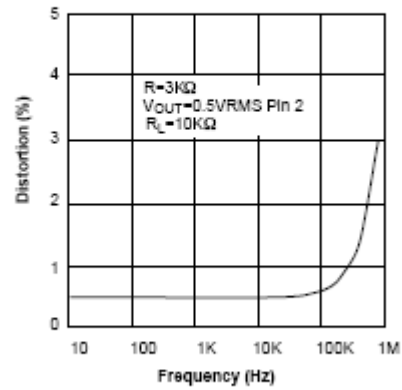


Figure 8. Sine Wave Distortion versus Operating Frequency with

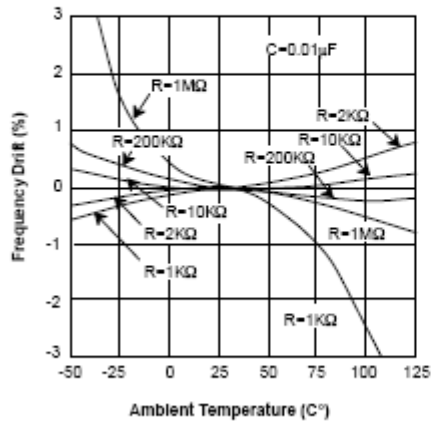


Figure 9. Frequency Drift versus Temperature.

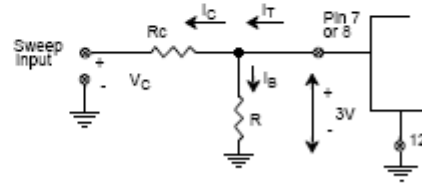
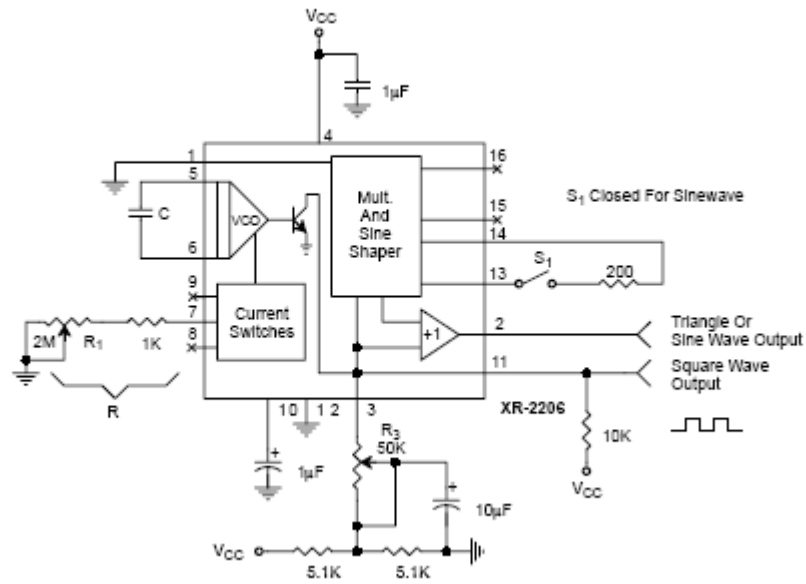


Figure 10. Circuit Connection for Frequency Sweep.



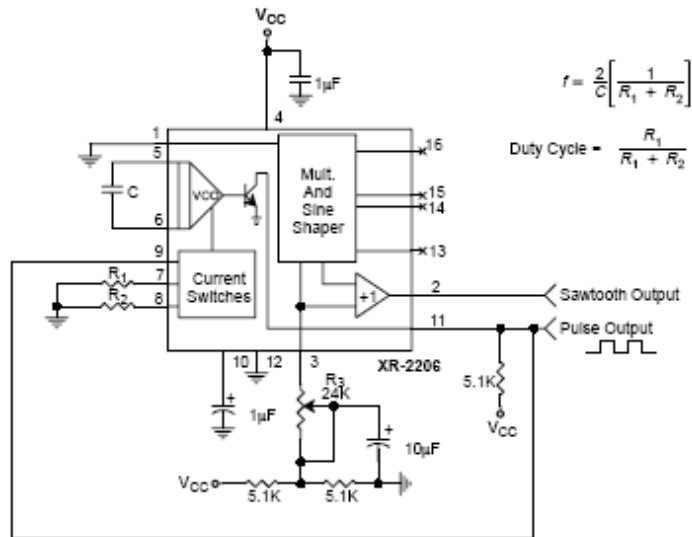


Figure 14. Circuit for Pulse and Ramp Generation.

Frequency-Shift Keying

The XR-2206 can be operated with two separate timing resistors, R_1 and R_2 , connected to the timing Pin 7 and 8, respectively, as shown in Figure 13. Depending on the polarity of the logic signal at Pin 9, either one or the other of these timing resistors is activated. If Pin 9 is open-circuited or connected to a bias voltage $\geq 2V$, only R_1 is activated. Similarly, if the voltage level at Pin 9 is $\leq 1V$, only R_2 is activated. Thus, the output frequency can be keyed between two levels, f_1 and f_2 , as:

$$f_1 = 1/R_1C \text{ and } f_2 = 1/R_2C$$

For split-supply operation, the keying voltage at Pin 9 is referenced to V^- .

Output DC Level Control

The dc level at the output (Pin 2) is approximately the same as the dc bias at Pin 3. In Figure 11, Figure 12 and Figure 13, Pin 3 is biased midway between V^+ and ground, to give an output dc level of $\approx V^+/2$.

APPLICATIONS INFORMATION

Sine Wave Generation

Without External Adjustment

Figure 11 shows the circuit connection for generating a sinusoidal output from the XR-2206. The potentiometer, R_1 at Pin 7, provides the desired frequency tuning. The maximum output swing is greater than $V^+/2$, and the typical distortion (THD) is $< 2.5\%$. If lower sine wave distortion is desired, additional adjustments can be provided as described in the following section.

The circuit of Figure 11 can be converted to split-supply operation, simply by replacing all ground connections with V^- . For split-supply operation, R_3 can be directly connected to ground.

With External Adjustment:

The harmonic content of sinusoidal output can be reduced to -0.5% by additional adjustments as shown in *Figure 12*. The potentiometer, R_A , adjusts the sine-shaping resistor, and R_B provides the fine adjustment for the waveform symmetry. The adjustment procedure is as follows:

1. Set R_B at midpoint and adjust R_A for minimum distortion.
2. With R_A set as above, adjust R_B to further reduce distortion.

Triangle Wave Generation

The circuits of *Figure 11* and *Figure 12* can be converted to triangle wave generation, by simply open-circuiting Pin 13 and 14 (i.e., S_1 open). Amplitude of the triangle is approximately twice the sine wave output.

FSK Generation

Figure 13 shows the circuit connection for sinusoidal FSK signal operation. Mark and space frequencies can be independently adjusted by the choice of timing resistors, R_1 and R_2 ; the output is phase-continuous during transitions. The keying signal is applied to Pin 9. The circuit can be converted to split-supply operation by simply replacing ground with V^- .

Pulse and Ramp Generation

Figure 14 shows the circuit for pulse and ramp waveform generation. In this mode of operation, the FSK keying terminal (Pin 9) is shorted to the square-wave output (Pin 11), and the circuit automatically frequency-shift keys itself between two separate frequencies during the positive-going and negative-going output waveforms. The pulse width and duty cycle can be adjusted from 1% to 99% by the choice of R_1 and R_2 . The values of R_1 and R_2 should be in the range of $1k\Omega$ to $2M\Omega$.

PRINCIPLES OF OPERATION**Description of Controls****Frequency of Operation:**

The frequency of oscillation, f_0 , is determined by the external timing capacitor, C , across Pin 5 and 8, and by the timing resistor, R , connected to either Pin 7 or 8. The frequency is given as:

$$f_0 = \frac{1}{RC} \text{ Hz}$$

and can be adjusted by varying either R or C . The recommended values of R , for a given frequency range, as shown in *Figure 5*. Temperature stability is optimum for $4k\Omega < R < 200k\Omega$. Recommended values of C are from $1000pF$ to $100\mu F$.

Frequency Sweep and Modulation:

Frequency of oscillation is proportional to the total timing current, I_T , drawn from Pin 7 or 8:

$$f = \frac{320I_T(\text{mA})}{C(\mu F)} \text{ Hz}$$

Timing terminals (Pin 7 or 8) are low-impedance points, and are internally biased at +3V, with respect to Pin 12. Frequency varies linearly with I_T , over a wide range of current values, from $1\mu A$ to $3mA$. The frequency can be controlled by applying a control voltage, V_C , to the activated timing pin as shown in *Figure 10*. The frequency of oscillation is related to V_C as:

$$f = \frac{1}{RC} \left(1 + \frac{R}{R_c} \left(1 - \frac{V_C}{3} \right) \right) \text{ Hz}$$

where V_C is in volts. The voltage-to-frequency conversion gain, K , is given as:

$$K = \partial f / \partial V_C = - \frac{0.32}{R_c C} \text{ Hz/V}$$

CAUTION: For safety operation of the circuit, I_T should be limited to $\leq 3mA$.

Output Amplitude:

Maximum output amplitude is inversely proportional to the external resistor, R_3 , connected to Pin 3 (see Figure 3). For sine wave output, amplitude is approximately 60mV peak per $k\Omega$ of R_3 ; for triangle, the peak amplitude is approximately 160mV peak per $k\Omega$ of R_3 . Thus, for example, $R_3 = 50k\Omega$ would produce approximately 13V sinusoidal output amplitude.

Amplitude Modulation:

Output amplitude can be modulated by applying a dc bias and a modulating signal to Pin 1. The internal impedance

at Pin 1 is approximately 100k Ω . Output amplitude varies linearly with the applied voltage at Pin 1, for values of dc bias at this pin, within 14 volts of $V_{CC}/2$ as shown in Figure 6. As this bias level approaches $V_{CC}/2$, the phase of the output signal is reversed, and the amplitude goes through zero. This property is suitable for phase-shift keying and suppressed-carrier AM generation. Total dynamic range of amplitude modulation is approximately 55dB.

CAUTION: AM control must be used in conjunction with a well-regulated supply, since the output amplitude now becomes a function of V_{CC} .

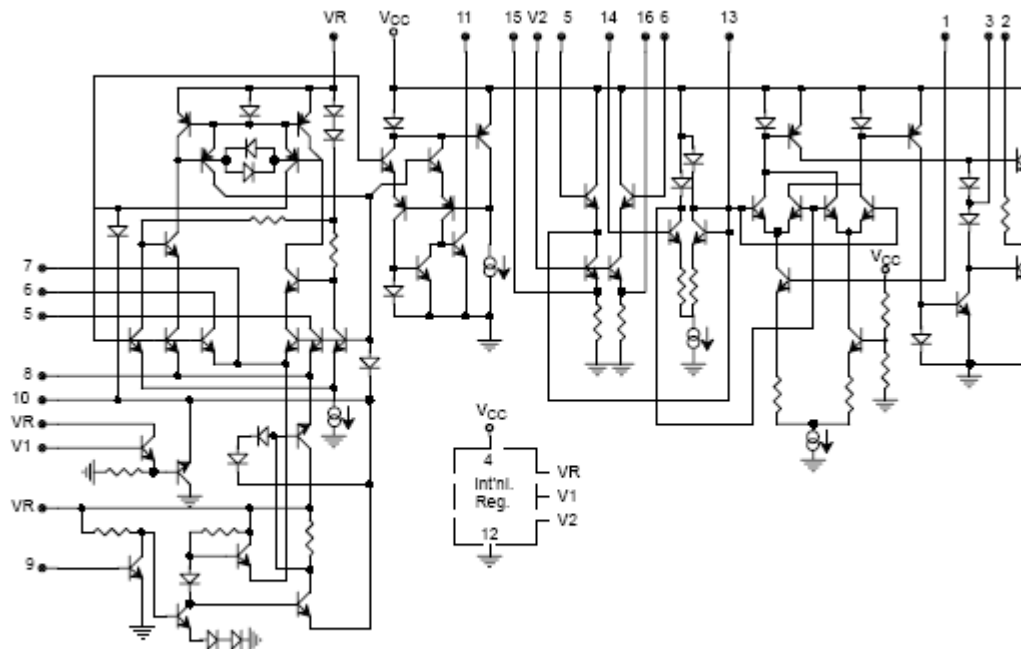
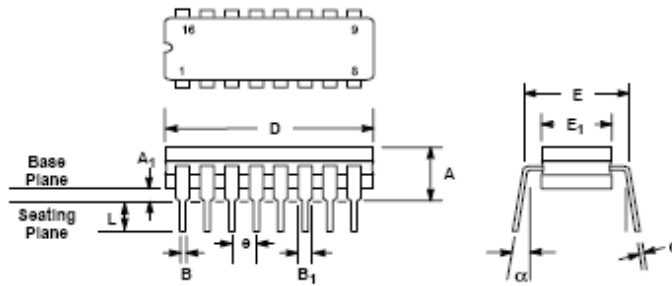


Figure 15. Equivalent Schematic Diagram

**16 LEAD CERAMIC DUAL-IN-LINE
(300 MIL CDIP)**

Rev. 1.00

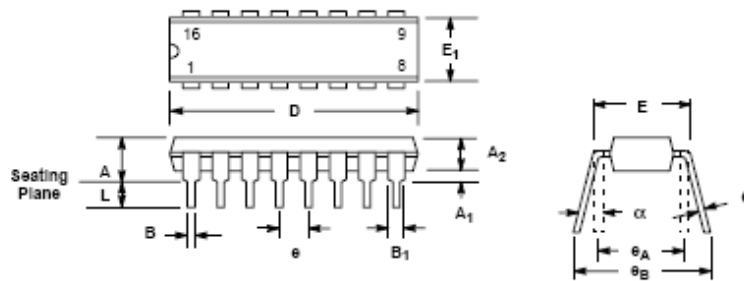


SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.100	0.200	2.54	5.08
A ₁	0.015	0.060	0.38	1.52
B	0.014	0.026	0.36	0.66
B ₁	0.045	0.065	1.14	1.65
c	0.008	0.018	0.20	0.46
D	0.740	0.840	18.80	21.34
E ₁	0.250	0.310	6.35	7.87
E	0.300 BSC		7.62 BSC	
e	0.100 BSC		2.54 BSC	
L	0.125	0.200	3.18	5.08
α	0° 15°		0° 15°	

Note: The control dimension is the Inch column

**16 LEAD PLASTIC DUAL-IN-LINE
(300 MIL PDIP)**

Rev. 1.00

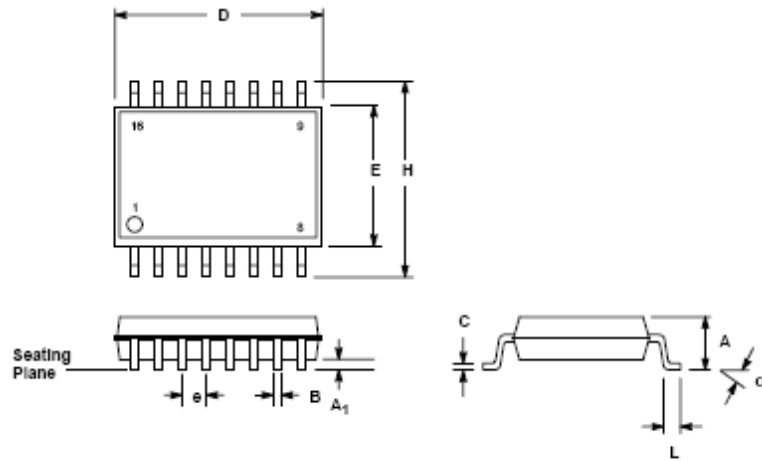


SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.145	0.210	3.68	5.33
A ₁	0.015	0.070	0.38	1.78
A ₂	0.115	0.195	2.92	4.95
B	0.014	0.024	0.36	0.56
B ₁	0.030	0.070	0.76	1.78
C	0.008	0.014	0.20	0.38
D	0.745	0.840	18.92	21.34
E	0.300	0.325	7.62	8.26
E ₁	0.240	0.280	6.10	7.11
e	0.100 BSC		2.54 BSC	
e _A	0.300 BSC		7.62 BSC	
e _B	0.310	0.430	7.87	10.92
L	0.115	0.160	2.92	4.06
α	0° 15°		0° 15°	

Note: The control dimension is the inch column

**16 LEAD SMALL OUTLINE
(300 MIL JEDEC SOIC)**

Rev. 1.00



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.093	0.104	2.35	2.65
A ₁	0.004	0.012	0.10	0.30
B	0.013	0.020	0.33	0.51
C	0.009	0.013	0.23	0.32
D	0.398	0.413	10.10	10.50
E	0.291	0.299	7.40	7.60
e	0.050 BSC		1.27 BSC	
H	0.394	0.419	10.00	10.65
L	0.016	0.050	0.40	1.27
α	0°	8°	0°	8°

Note: The control dimension is the millimeter column

FEATURES

- Wide Frequency Range, 0.01Hz to 300kHz
- Wide Supply Voltage Range, 4.5V to 20V
- HCMOS/TTL/Logic Compatibility
- FSK Demodulation, with Carrier Detection
- Wide Dynamic Range, 10mV to 3V rms
- Adjustable Tracking Range, $\pm 1\%$ to 80%
- Excellent Temp. Stability, $\pm 50\text{ppm}/^\circ\text{C}$, max.

APPLICATIONS

- Caller Identification Delivery
- FSK Demodulation
- Data Synchronization
- Tone Decoding
- FM Detection
- Carrier Detection

GENERAL DESCRIPTION

The XR-2211 is a monolithic phase-locked loop (PLL) system especially designed for data communications applications. It is particularly suited for FSK modem applications. It operates over a wide supply voltage range of 4.5 to 20V and a wide frequency range of 0.01Hz to 300kHz. It can accommodate analog signals between 10mV and 3V, and can interface with conventional DTL, TTL, and ECL logic families. The circuit consists of a basic PLL for tracking an input signal within the pass band, a

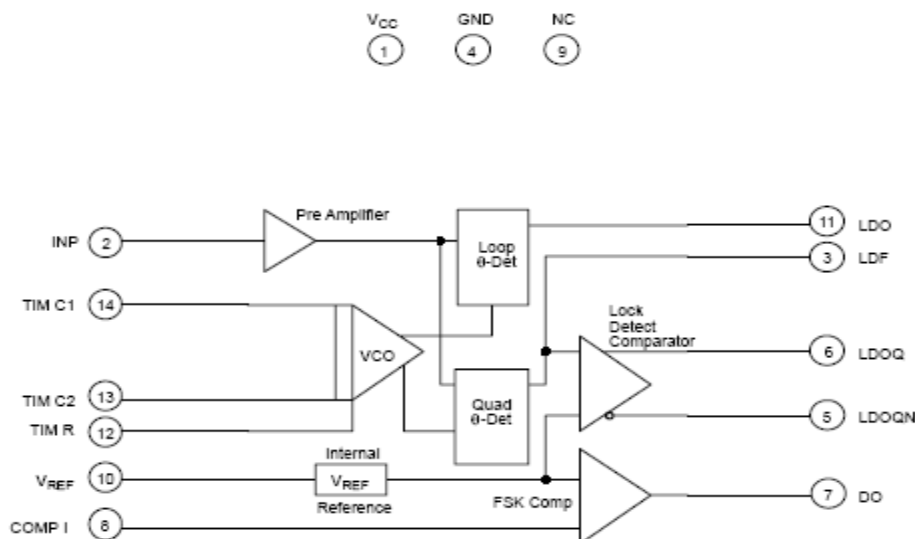
quadrature phase detector which provides carrier detection, and an FSK voltage comparator which provides FSK demodulation. External components are used to independently set center frequency, bandwidth, and output delay. An internal voltage reference proportional to the power supply is provided at an output pin.

The XR-2211 is available in 14 pin packages specified for military and industrial temperature ranges.

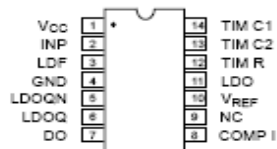
ORDERING INFORMATION

Part No.	Package	Operating Temperature Range
XR-2211M	14 Pin CDIP (0.300")	-55°C to +125°C
XR-2211N	14 Pin CDIP (0.300")	-40°C to +85°C
XR-2211P	14 Pin PDIP (0.300")	-40°C to +85°C
XR-2211D	14 Lead SOIC (Jedec, 0.150")	-40°C to +85°C

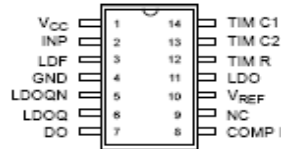
BLOCK DIAGRAM



PIN CONFIGURATION



14 Lead CDIP, PDIP (0.300")



14 Lead SOIC (Jedec, 0.150")

PIN DESCRIPTION

Pin #	Symbol	Type	Description
1	V _{CC}	I	Positive Power Supply.
2	INP	I	Receive Analog Input.
3	LDF	O	Lock Detect Filter.
4	GND		Ground Pin.
5	LDOQN	O	Lock Detect Output Not. This output will be low if the VCO is in the capture range.
6	LDOQ	O	Lock Detect Output. This output will be high if the VCO is in the capture range.
7	DO	O	Data Output. Decoded FSK output.
8	COMP I	I	FSK Comparator Input.
9	NC		Not Connected.
10	V _{REF}	O	Internal Voltage Reference. The value of V _{REF} is V _{CC} /2 - 650mV.
11	LDO	O	Loop Detect Output. This output provides the result of the quadrature phase detection.
12	TIM R	I	Timing Resistor Input. This pin connects to the timing resistor of the VCO.
13	TIM C2	I	Timing Capacitor Input. The timing capacitor connects between this pin and pin 14.
14	TIM C1	I	Timing Capacitor Input. The timing capacitor connects between this pin and pin 13.

XR-2211



ELECTRICAL CHARACTERISTICS

Test Conditions: $V_{CC} = 12V$, $T_A = +25^\circ C$, $R_O = 30K\Omega$, $C_O = 0.033\mu F$, unless otherwise specified.

Parameter	Min.	Typ.	Max.	Unit	Conditions
General					
Supply Voltage	4.5		20	V	
Supply Current		4	7	mA	$R_O \geq 10K\Omega$. See Figure 4.
Oscillator Section					
Frequency Accuracy		± 1	± 3	%	Deviation from $f_O = 1/R_O C_O$
Frequency Stability					
Temperature		± 20	± 50	ppm/ $^\circ C$	See Figure 8.
Power Supply		0.05	0.5	%/V	$V_{CC} = 12 \pm 1V$. See Figure 7.
		0.2		%/V	$V_{CC} = \pm 5V$. See Figure 7.
Upper Frequency Limit	100	300		kHz	$R_O = 8.2K\Omega$, $C_O = 400pF$
Lowest Practical Operating Frequency			0.01	Hz	$R_O = 2M\Omega$, $C_O = 50\mu F$
Timing Resistor, R_O - See Figure 5					
Operating Range	5		2000	K Ω	
Recommended Range	5			K Ω	See Figure 7 and Figure 8.
Loop Phase Detector Section					
Peak Output Current	± 150	± 200	± 300	μA	Measured at Pin 11
Output Offset Current		1		μA	
Output Impedance		1		M Ω	
Maximum Swing	± 4	± 5		V	Referenced to Pin 10
Quadrature Phase Detector					
					Measured at Pin 3
Peak Output Current	100	300		μA	
Output Impedance		1		M Ω	
Maximum Swing		11		V _{PP}	
Input Preamp Section					
					Measured at Pin 2
Input Impedance		20		K Ω	
Input Signal					
Voltage Required to Cause Limiting		2	10	mV rms	

Notes

Parameters are guaranteed over the recommended operating conditions, but are not 100% tested in production. Bold face parameters are covered by production test and guaranteed over operating temperature range.

DC ELECTRICAL CHARACTERISTICS (CONT'D)

Test Conditions: $V_{CC} = 12V$, $T_A = +25^\circ C$, $R_O = 30K\Omega$, $C_O = 0.033\mu F$, unless otherwise specified.

Parameter	Min.	Typ.	Max.	Unit	Conditions
Voltage Comparator Section					
Input Impedance		2		M Ω	Measured at Pins 3 and 8
Input Bias Current		100		nA	
Voltage Gain	55	70		dB	$R_L = 5.1K\Omega$
Output Voltage Low		300	500	mV	$I_C = 3mA$
Output Leakage Current		0.01	10	μA	$V_O = 20V$
Internal Reference					
Voltage Level	4.9	5.3	5.7	V	Measured at Pin 10
Output Impedance		100		Ω	AC Small Signal
Maximum Source Current		80		μA	

Notes

Parameters are guaranteed over the recommended operating conditions, but are not 100% tested in production. Bold face parameters are covered by production test and guaranteed over operating temperature range.

Specifications are subject to change without notice

ABSOLUTE MAXIMUM RATINGS

Power Supply 20V
 Input Signal Level 3V rms
 Power Dissipation 900mW

Package Power Dissipation Ratings

CDIP 750mW
 Derate Above $T_A = 25^\circ C$ 8mW/ $^\circ C$
 PDIP 800mW
 Derate Above $T_A = 25^\circ C$ 60mW/ $^\circ C$
 SOIC 390mW
 Derate Above $T_A = 25^\circ C$ 5mW/ $^\circ C$

SYSTEM DESCRIPTION

The main PLL within the XR-2211 is constructed from an input preamplifier, analog multiplier used as a phase detector and a precision voltage controlled oscillator (VCO). The preamplifier is used as a limiter such that input signals above typically 10mV rms are amplified to a constant high level signal. The multiplying-type phase detector acts as a digital exclusive or gate. Its output (unfiltered) produces sum and difference frequencies of the input and the VCO output. The VCO is actually a current controlled oscillator with its normal input current (I_O) set by a resistor (R_O) to ground and its driving current with a resistor (R_I) from the phase detector.

The output of the phase detector produces sum and difference of the input and the VCO frequencies

(internally connected). When in lock, these frequencies are $f_{IN} + f_{VCO}$ (2 times f_{IN} when in lock) and $f_{IN} - f_{VCO}$ (0Hz when lock). By adding a capacitor to the phase detector output, the 2 times f_{IN} component is reduced, leaving a DC voltage that represents the phase difference between the two frequencies. This closes the loop and allows the VCO to track the input frequency.

The FSK comparator is used to determine if the VCO is driven above or below the center frequency (FSK comparator). This will produce both active high and active low outputs to indicate when the main PLL is in lock (quadrature phase detector and lock detector comparator).

PRINCIPLES OF OPERATION

Signal Input (Pin 2): Signal is AC coupled to this terminal. The internal impedance at pin 2 is 20kΩ. Recommended input signal level is in the range of 10mV rms to 3V rms.

Quadrature Phase Detector Output (Pin 3): This is the high impedance output of quadrature phase detector and is internally connected to the input of lock detect voltage comparator. In tone detection applications, pin 3 is connected to ground through a parallel combination of R_D and C_D (see Figure 3) to eliminate the chatter at lock detect outputs. If the tone detect section is not used, pin 3 can be left open.

Lock Detect Output, Q (Pin 6): The output at pin 6 is at "low" state when the PLL is out of lock and goes to "high" state when the PLL is locked. It is an open collector type output and requires a pull-up resistor, R_L , to V_{CC} for proper operation. At "low" state, it can sink up to 5mA of load current.

Lock Detect Complement, (Pin 5): The output at pin 5 is the logic complement of the lock detect output at pin 6. This output is also an open collector type stage which can sink 5mA of load current at low or "on" state.

FSK Data Output (Pin 7): This output is an open collector logic stage which requires a pull-up resistor, R_L , to V_{CC} for proper operation. It can sink 5mA of load current. When decoding FSK signals, FSK data output is at "high" or "off" state for low input frequency, and at "low" or "on" state for high input frequency. If no input signal is present, the logic state at pin 7 is indeterminate.

FSK Comparator Input (Pin 8): This is the high impedance input to the FSK voltage comparator. Normally, an FSK post-detection or data filter is connected between this terminal and the PLL phase detector output (pin 11). This data filter is formed by R_F and C_F (see Figure 3). The threshold voltage of the comparator is set by the internal reference voltage, V_{REF} , available at pin 10.

Reference Voltage, V_{REF} (Pin 10): This pin is internally biased at the reference voltage level, V_{REF} : $V_{REF} = V_{CC}/2 - 850mV$. The DC voltage level at this pin forms an internal reference for the voltage levels at pins 5, 6, 11 and 12. Pin

10 must be bypassed to ground with a 0.1μF capacitor for proper operation of the circuit.

Loop Phase Detector Output (Pin 11): This terminal provides a high impedance output for the loop phase detector. The PLL loop filter is formed by R_1 and C_1 connected to pin 11 (see Figure 3.) With no input signal, or with no phase error within the PLL, the DC level at pin 11 is very nearly equal to V_{REF} . The peak to peak voltage swing available at the phase detector output is equal to $2 \times V_{REF}$.

VCO Control Input (Pin 12): VCO free-running frequency is determined by external timing resistor, R_D , connected from this terminal to ground. The VCO free-running frequency, f_0 , is:

$$f_0 = \frac{1}{R_D \cdot C_D} \text{ Hz}$$

where C_D is the timing capacitor across pins 13 and 14. For optimum temperature stability, R_D must be in the range of 10kΩ to 100kΩ (see Figure 8.)

This terminal is a low impedance point, and is internally biased at a DC level equal to V_{REF} . The maximum timing current drawn from pin 12 must be limited to $\leq 3mA$ for proper operation of the circuit.

VCO Timing Capacitor (Pins 13 and 14): VCO frequency is inversely proportional to the external timing capacitor, C_D , connected across these terminals (see Figure 8.) C_D must be non-polar, and in the range of 200pF to 10μF.

VCO Frequency Adjustment: VCO can be fine-tuned by connecting a potentiometer, R_X , in series with R_D at pin 12 (see Figure 10.)

VCO Free-Running Frequency, f_0 : XR-2211 does not have a separate VCO output terminal. Instead, the VCO outputs are internally connected to the phase detector sections of the circuit. For set-up or adjustment purposes, the VCO free-running frequency can be tuned by using the generalized circuit in Figure 3, and applying an alternating bit pattern of 0's and 1's at the known mark and space frequencies. By adjusting R_D , the VCO can then be tuned to obtain a 50% duty cycle on the FSK output (pin 7). This will ensure that the VCO f_0 value is accurately referenced to the mark and space frequencies.

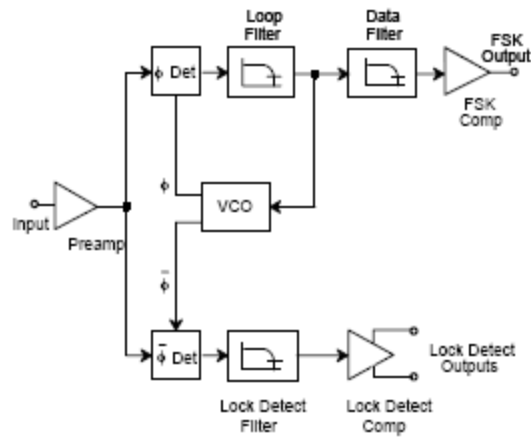


Figure 2. Functional Block Diagram of a Tone and FSK Decoding System Using XR-2211

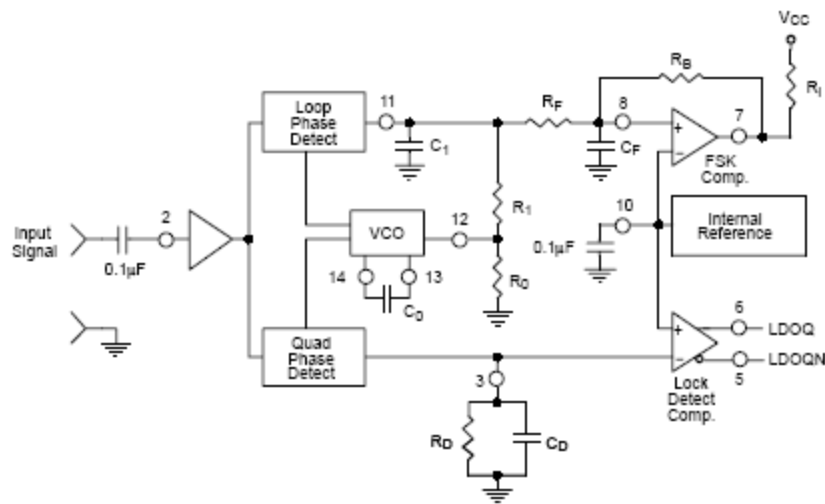


Figure 3. Generalized Circuit Connection for FSK and Tone Detection

DESIGN EQUATIONS

(All resistance in Ω , all frequency in Hz and all capacitance in farads, unless otherwise specified)

(See *Figure 3* for definition of components)

1. VCO Center Frequency, f_0 :

$$f_0 = \frac{1}{R_0 \cdot C_0}$$

2. Internal Reference Voltage, V_{REF} (measured at pin 10):

$$V_{REF} = \left(\frac{V_{CC}}{2} \right) - 650mV \text{ in volts}$$

3. Loop Low-Pass Filter Time Constant, τ :

$$\tau = C_1 \cdot R_{pp} \text{ (seconds)}$$

where:

$$R_{pp} = \left(\frac{R_1 \cdot R_f}{R_1 + R_f} \right)$$

if R_f is ∞ or C_f reactance is ∞ , then $R_{pp} = R_1$

4. Loop Damping, ζ :

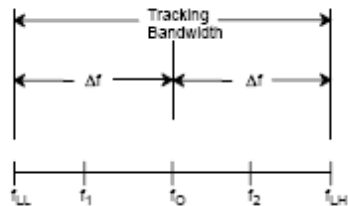
$$\zeta = \sqrt{\left(\frac{1250 \cdot C_0}{R_1 \cdot C_1} \right)}$$

Note: For derivation/explanation of this equation, please see TAN-011.

5. Loop-tracking

bandwidth, $\pm = \frac{\Delta f}{f_0}$

$$\frac{\Delta f}{f_0} = \frac{R_0}{R_1}$$



6. FSK Data filter time constant, t_F :

$$t_F = \frac{R_B \cdot R_F}{(R_B + R_F)} \cdot C_F \text{ (seconds)}$$

7. Loop phase detector conversion gain, K_d : (K_d is the differential DC voltage across pin 10 and pin 11, per unit of phase error at phase detector input):

$$K_d = \frac{V_{REF} \cdot R_1}{10,000 \cdot \pi} \left[\frac{\text{volt}}{\text{radian}} \right]$$

Note: For derivation/explanation of this equation, please see TAN-011.

8. VCO conversion gain, K_o : (K_o is the amount of change in VCO frequency, per unit of DC voltage change at pin 11):

$$K_o = \frac{-2\pi}{V_{REF} \cdot C_0 \cdot R_1} = \left(\frac{\text{radian/second}}{\text{volt}} \right)$$

9. The filter transfer function:

$$F(s) = \frac{1}{1 + sR_1 \cdot C_1} \text{ at } 0 \text{ Hz.} \quad S = j\omega \text{ and } \omega = 0$$

10. Total loop gain, K_T :

$$K_T = K_o \cdot K_d \cdot F(s) = \left(\frac{R_F}{5,000 \cdot C_0 \cdot (R_1 + R_F)} \right) \left[\frac{1}{\text{seconds}} \right]$$

11. Peak detector current I_A :

$$I_A = \frac{V_{REF}}{20,000} \text{ (} V_{REF} \text{ in volts and } I_A \text{ in amps)}$$

Note: For derivation/explanation of this equation, please see TAN-011.

APPLICATIONS INFORMATION

FSK Decoding

Figure 10 shows the basic circuit connection for FSK decoding. With reference to Figure 3 and Figure 10, the functions of external components are defined as follows: R_0 and C_0 set the PLL center frequency, R_1 sets the system bandwidth, and C_1 sets the loop filter time constant and the loop damping factor. C_F and R_F form a one-pole post-detection filter for the FSK data output. The resistor R_B from pin 7 to pin 8 introduces positive feedback across the FSK comparator to facilitate rapid transition between output logic states.

Design Instructions:

The circuit of Figure 10 can be tailored for any FSK decoding application by the choice of five key circuit components: R_0 , R_1 , C_0 , C_1 and C_F . For a given set of FSK mark and space frequencies, f_0 and f_1 , these parameters can be calculated as follows:

(All resistance in Ω 's, all frequency in Hz and all capacitance in farads, unless otherwise specified)

- a) Calculate PLL center frequency, f_0 :

$$f_0 = \sqrt{F_1 \cdot F_2}$$

- b) Choose value of timing resistor R_0 , to be in the range of 10K Ω to 100K Ω . This choice is arbitrary. The recommended value is $R_0 = 20K\Omega$. The final value of R_0 is normally fine-tuned with the series potentiometer, R_X .

$$R_0 = R_0 + \frac{R_X}{2}$$

- c) Calculate value of C_0 from design equation (1) or from Figure 7:

$$C_0 = \frac{1}{R_0 \cdot f_0}$$

- d) Calculate R_1 to give the desired tracking bandwidth (See design equation 5).

$$R_1 = \frac{R_0 \cdot f_0}{(f_1 - f_2)} \cdot 2$$

- e) Calculate C_1 to set loop damping. (See design equation 4):

Normally, $\zeta = 0.5$ is recommended.

$$C_1 = \frac{1250 \cdot C_0}{R_1 \cdot \zeta^2}$$

- f) The input to the XR-2211 may sometimes be too sensitive to noise conditions on the input line. Figure 4 illustrates a method of de-sensitizing the XR-2211 from such noisy line conditions by the use of a resistor, R_x , connected from pin 2 to ground. The value of R_x is chosen by the equation and the desired minimum signal threshold level.

$$V_{IN} \text{ minimum (peak)} = V_a - V_b = \Delta V \pm 2.8mV \text{ offset} = V_{REF} \frac{20,000}{(20,000 + R_x)} \text{ or } R_x = 20,000 \left(\frac{V_{REF}}{\Delta V} - 1 \right)$$

V_{IN} minimum (peak) input voltage must exceed this value to be detected (equivalent to adjusting V threshold)

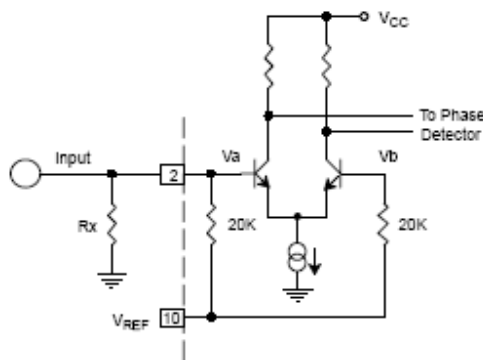


Figure 4. Desensitizing Input Stage

- g) Calculate Data Filter Capacitance, C_F :

$$R_{sum} = \frac{(R_f + R_1) \cdot R_B}{(R_1 + R_f + R_B)}$$

$$C_F = \frac{0.25}{(R_{sum} \cdot \text{Baud Rate})} \quad \text{Baud rate in } \frac{1}{\text{seconds}}$$

Note: All values except R_0 can be rounded to nearest standard value.

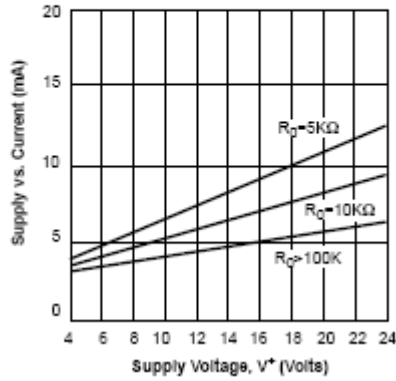


Figure 5. Typical Supply Current vs. V+ (Logic Outputs Open Circuited)

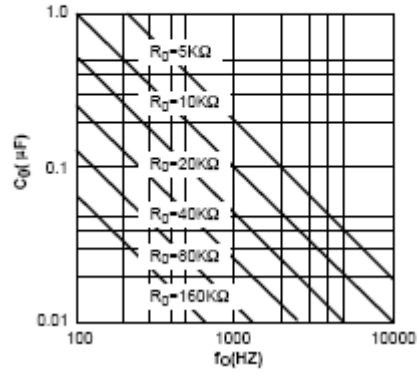


Figure 6. VCO Frequency vs. Timing Resistor

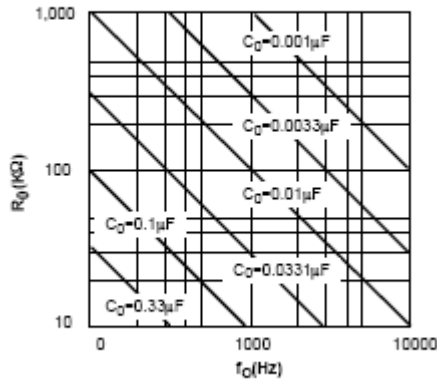


Figure 7. VCO Frequency vs. Timing Capacitor

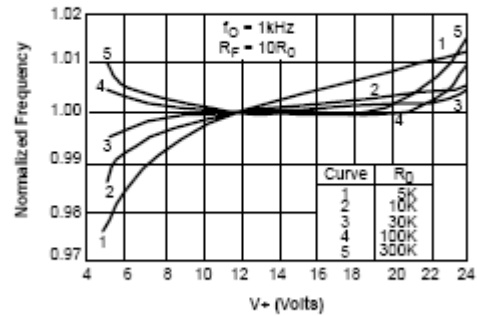


Figure 8. Typical f_0 vs. Power Supply Characteristics

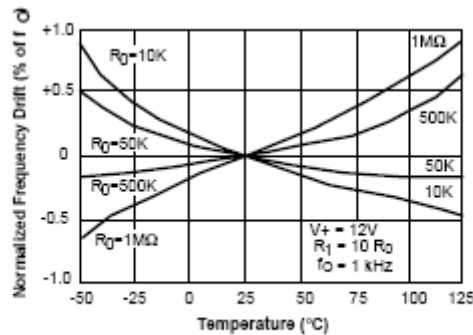


Figure 9. Typical Center Frequency Drift vs. Temperature

Design Example:

1200 Baud FSK demodulator with mark and space frequencies of 1200/2200.

Step 1: Calculate f_0 : from design instructions

$$(a) f_0 = \sqrt{1200 \cdot 2200} = 1624$$

Step 2: Calculate R_0 : $R_0 = 10K$ with a potentiometer of 10K. (See design instructions (b))

$$(b) R_T = 10 + \left(\frac{10}{2}\right) = 15K$$

Step 3: Calculate C_0 from design instructions

$$(c) C_0 = \frac{1}{15000 \cdot 1624} = 39nF$$

Step 4: Calculate R_1 : from design instructions

$$(d) R_1 = \frac{20000 \cdot 1624 \cdot 2}{(2200 - 1200)} = 51,000$$

Step 5: Calculate C_1 : from design instructions

$$(e) C_1 = \frac{1250 \cdot 39nF}{51000 \cdot 0.5^2} = 3.9nF$$

Step 6: Calculate R_F : R_F should be at least five times R_1 , $R_F = 51,000 \cdot 5 = 255 K\Omega$

Step 7: Calculate R_B : R_B should be at least five times R_F , $R_B = 255,000 \cdot 5 = 1.2 M\Omega$

Step 8: Calculate R_{SUM} :

$$R_{SUM} = \frac{(R_F + R_1) \cdot R_B}{(R_F + R_1 + R_B)} = 240K\Omega$$

Step 9: Calculate C_F :

$$C_F = \frac{0.25}{(R_{SUM} \cdot \text{Baud Rate})} = 1nF$$

Note: All values except R_0 can be rounded to nearest standard value.

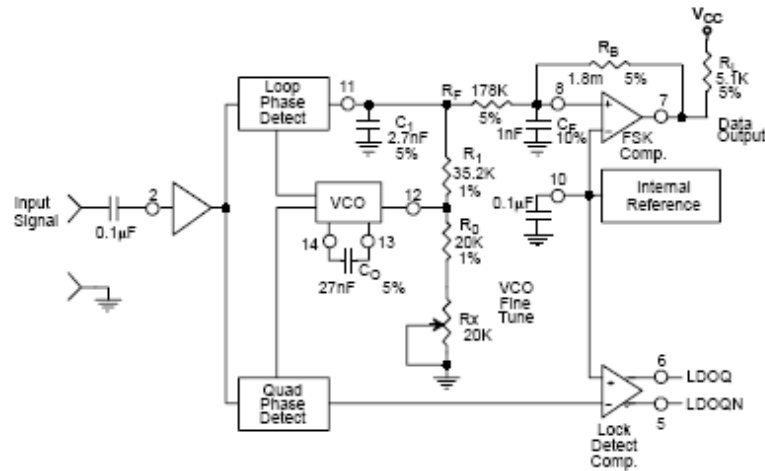


Figure 10. Circuit Connection for FSK Decoding of Caller Identification Signals (Bell 202 Format)

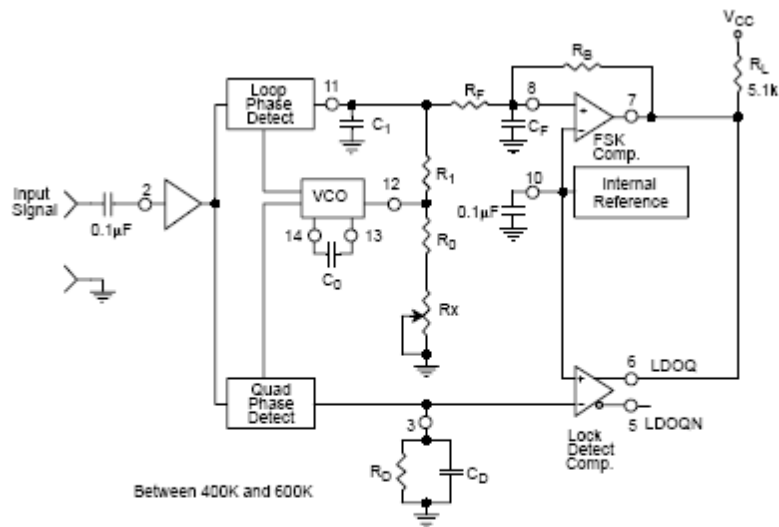


Figure 11. External Connectors for FSK Demodulation with Carrier Detect Capability

Design Instructions:

The circuit of *Figure 12* can be optimized for any tone detection application by the choice of the 5 key circuit components: R_0 , R_1 , C_0 , C_1 and C_D . For a given input, the tone frequency, f_S , these parameters are calculated as follows:

(All resistance in Ω 's, all frequency in Hz and all capacitance in farads, unless otherwise specified)

- Choose value of timing resistor R_0 to be in the range of 10K Ω to 50K Ω . This choice is dictated by the max./min. current that the internal voltage reference can deliver. The recommended value is $R_0 = 20\text{K}\Omega$. The final value of R_0 is normally fine-tuned with the series potentiometer, R_X .
- Calculate value of C_0 from design equation (1) or from *Figure 7* $f_S = f_0$:

$$C_0 = \frac{1}{R_0 \cdot f_S}$$

- Calculate R_1 to set the bandwidth $\pm\Delta f$ (See design equation 5):

$$R_1 = \frac{R_0 \cdot f_0 \cdot 2}{\Delta f}$$

Note: The total detection bandwidth covers the frequency range of $f_0 \pm \Delta f$

- Calculate value of C_1 for a given loop damping factor:

Normally, $\zeta = 0.5$ is recommended.

$$C_1 = \frac{1250 \cdot C_0}{R_1 \cdot \zeta^2}$$

Increasing C_1 improves the out-of-band signal rejection, but increases the PLL capture time.

- Calculate value of the filter capacitor C_D . To avoid chatter at the logic output, with $R_D = 470\text{K}\Omega$, C_D must be:

$$C_D > \frac{16}{\Delta f} \quad C \text{ in } \mu F$$

Increasing C_D slows down the logic output response time.

Design Examples:

Tone detector with a detection band of $\pm 100\text{Hz}$:

- Choose value of timing resistor R_0 to be in the range of 10K Ω to 50K Ω . This choice is dictated by the max./min. current that the internal voltage reference can deliver. The recommended value is $R_0 = 20\text{K}\Omega$. The final value of R_0 is normally fine-tuned with the series potentiometer, R_X .
- Calculate value of C_0 from design equation (1) or from *Figure 8* $f_S = f_0$:

$$C_0 = \frac{1}{R_0 \cdot f_S} = \frac{1}{20,000 \cdot 1,000} = 50\text{nF}$$

c) Calculate R_1 to set the bandwidth $\pm\Delta f$ (See design equation 5):

$$R_1 = \frac{R_0 \cdot f_0 \cdot 2}{\Delta f} = \frac{20,000 \cdot 1,000 \cdot 2}{100} = 400K$$

Note: The total detection bandwidth covers the frequency range of $f_0 \pm \Delta f$

d) Calculate value of C_0 for a given loop damping factor:

Normally, $\zeta = 0.5$ is recommended.

$$C_1 = \frac{1250 \cdot C_0}{R_1 \zeta^2} = \frac{1250 \cdot 50 \cdot 10^{-9}}{400,000 \cdot 0.5^2} = 8.25pF$$

Increasing C_1 improves the out-of-band signal rejection, but increases the PLL capture time.

e) Calculate value of the filter capacitor C_D . To avoid chatter at the logic output, with $R_D = 470K\Omega$, C_D must be:

$$C_D = \frac{16}{\Delta f} \geq \frac{16}{200} \geq 80nF$$

Increasing C_D slows down the logic output response time.

f) Fine tune center frequency with $5K\Omega$ potentiometer, R_X .

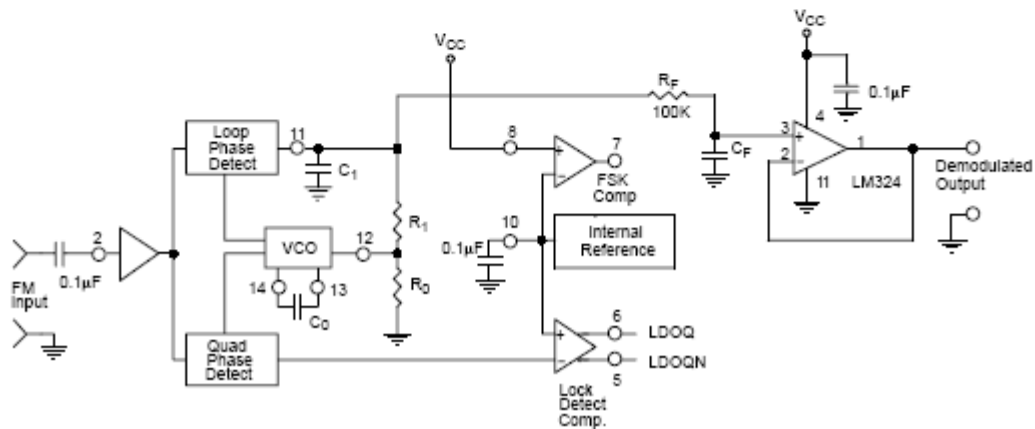


Figure 13. Linear FM Detector Using XR-2211 and an External Op Amp.
(See Section on Design Equation for Component Values.)

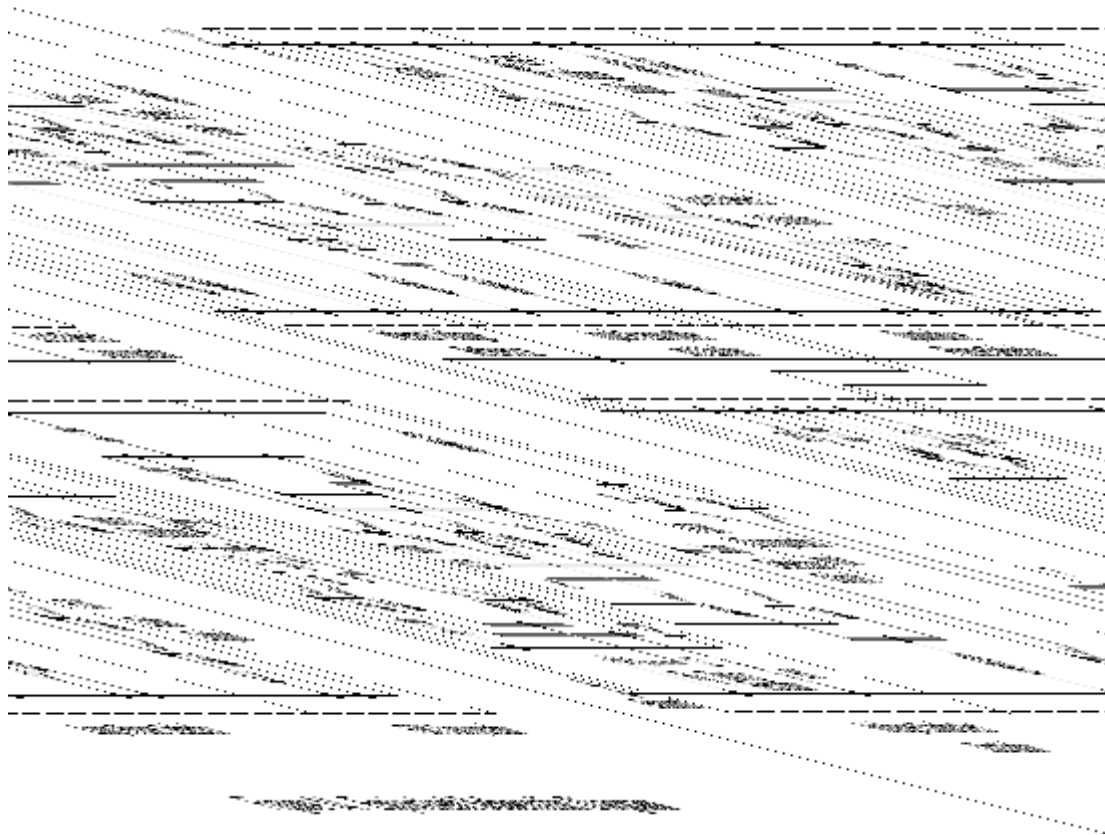
Linear FM Detection

XR-2211 can be used as a linear FM detector for a wide range of analog communications and telemetry applications. The recommended circuit connection for this application is shown in *Figure 13*. The demodulated output is taken from the loop phase detector output (pin 11), through a post-detection filter made up of R_F and C_F , and an external buffer amplifier. This buffer amplifier is necessary because of the high impedance output at pin 11. Normally, a non-inverting unity gain op amp can be used as a buffer amplifier, as shown in *Figure 13*.

The FM detector gain, i.e., the output voltage change per unit of FM deviation can be given as:

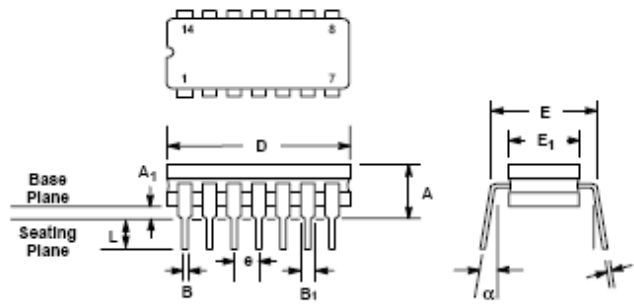
$$V_{OUT} = \frac{R_1 \cdot V_{REF}}{100 \cdot R_0}$$

where V_R is the internal reference voltage ($V_{REF} = V_{CC}/2 - 650mV$). For the choice of external components R_1 , R_0 , C_D , C_1 and C_F , see the section on design equations.



**14 LEAD CERAMIC DUAL-IN-LINE
(300 MIL CDIP)**

Rev. 1.00

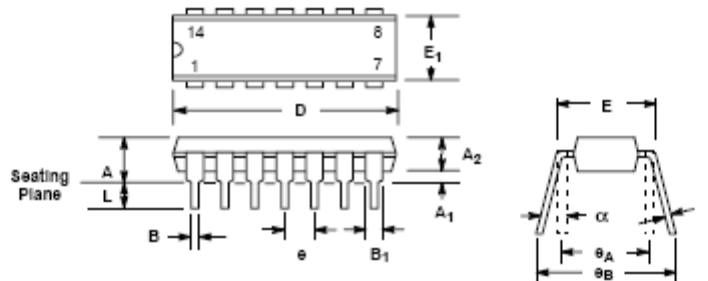


SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.100	0.200	2.54	5.08
A ₁	0.015	0.060	0.38	1.52
B	0.014	0.026	0.36	0.66
B ₁	0.045	0.065	1.14	1.65
c	0.008	0.018	0.20	0.46
D	0.685	0.785	17.40	19.94
E ₁	0.250	0.310	6.35	7.87
E	0.300 BSC		7.62 BSC	
e	0.100 BSC		2.54 BSC	
L	0.125	0.200	3.18	5.08
α	0°	15°	0°	15°

Note: The control dimension is the Inch column

14 LEAD PLASTIC DUAL-IN-LINE (300 MIL PDIP)

Rev. 1.00

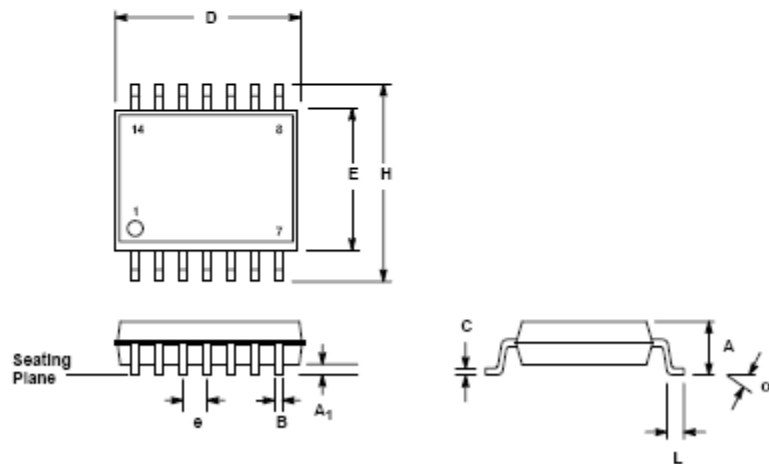


SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.145	0.210	3.68	5.33
A ₁	0.015	0.070	0.38	1.78
A ₂	0.115	0.195	2.92	4.95
B	0.014	0.024	0.36	0.56
B ₁	0.030	0.070	0.76	1.78
C	0.008	0.014	0.20	0.36
D	0.725	0.795	18.42	20.19
E	0.300	0.325	7.62	8.26
E ₁	0.240	0.280	6.10	7.11
e	0.100 BSC		2.54 BSC	
e _A	0.300 BSC		7.62 BSC	
e _B	0.310	0.430	7.87	10.92
L	0.115	0.160	2.92	4.06
α	0° 15°		0° 15°	

Note: The control dimension is the Inch column

**14 LEAD SMALL OUTLINE
(150 MIL JEDEC SOIC)**

Rev. 1.00



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.053	0.069	1.35	1.75
A ₁	0.004	0.010	0.10	0.25
B	0.013	0.020	0.33	0.51
C	0.007	0.010	0.19	0.25
D	0.337	0.344	8.55	8.75
E	0.150	0.157	3.80	4.00
e	0.050 BSC		1.27 BSC	
H	0.228	0.244	5.80	6.20
L	0.016	0.050	0.40	1.27
α	0°	8°	0°	8°

Note: The control dimension is the millimeter column